

# TLV2186 精密、轨至轨输入和输出、24V、零漂移运算放大器

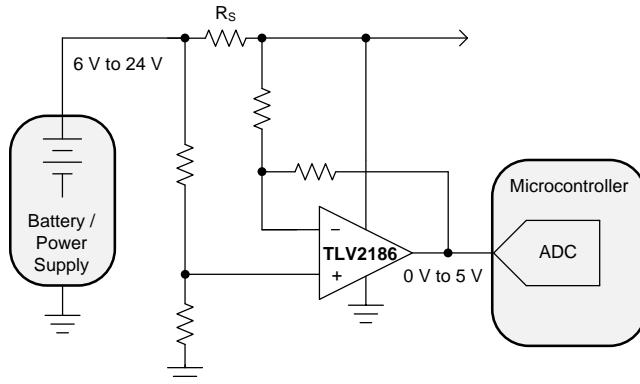
## 1 特性

- 高精度:
  - 温漂:  $0.1\mu\text{V}/^\circ\text{C}$
  - 低失调电压:  $10\mu\text{V}$
- 低静态电流:  $90\mu\text{A}$
- 出色的动态性能:
  - 增益带宽:  $750\text{kHz}$
  - 压摆率:  $0.35\text{V}/\mu\text{s}$
- 强大设计:
  - RFI/EMI 滤波输入
- 轨至轨输入/输出
- 电源电压范围: 4.5V 至 24V

## 2 应用

- 精密高侧电流检测
- 桥式放大器
- 应变仪
- 温度测量
- 电阻式温度检测器
- 称重计
- 测热仪表
- 电源

### 高侧电流分流监控器应用



## 3 说明

TLV2186 是一款低功耗、24V、轨至轨输入和输出的零漂移运算放大器。TLV2186 具有仅  $10\mu\text{V}$  的典型失调电压和  $0.1\mu\text{V}/^\circ\text{C}$  的典型失调电压温漂。该器件非常适合精密仪表、信号测量和有源滤波应用。

TLV2186 具有低静态电流消耗 ( $90\mu\text{A}$ )，非常适合功率敏感型应用，如电池供电和便携式系统。

此外，高共模架构以及低失调电压可实现正电源轨的高侧电流分流监控。该器件还在运输、装卸和组装期间提供强大的 ESD 保护。

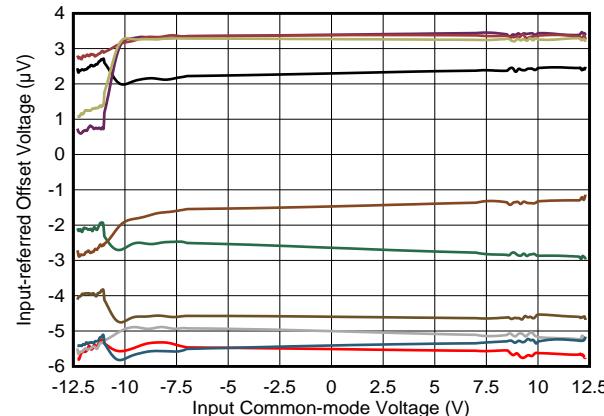
此器件的额定工作温度范围为  $-40^\circ\text{C}$  至  $+125^\circ\text{C}$ 。

### 器件信息<sup>(1)</sup>

| 器件型号    | 封装       | 封装尺寸 (标称值)      |
|---------|----------|-----------------|
| TLV2186 | SOIC (8) | 4.90mm × 3.90mm |

(1) 如需了解所有可用封装，请参阅数据表末尾的封装选项附录。

### $V_{OS}$ 与输入共模电压



本文档旨在为方便起见，提供有关 TI 产品中文版本的信息，以确认产品的概要。有关适用的官方英文版本的最新信息，请访问 [www.ti.com](http://www.ti.com)，其内容始终优先。TI 不保证翻译的准确性和有效性。在实际设计之前，请务必参考最新版本的英文版本。

## 目录

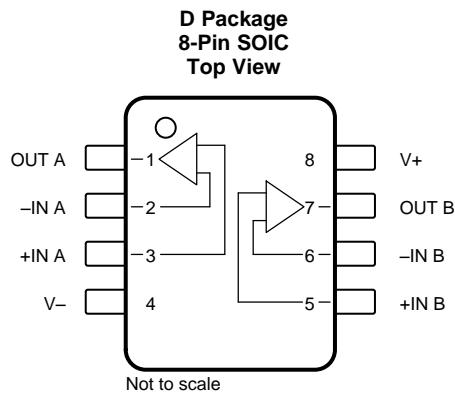
|          |  |           |           |                                       |           |
|----------|--|-----------|-----------|---------------------------------------|-----------|
| <b>1</b> | <b>特性</b>                              | <b>1</b>  | <b>8</b>  | <b>Application and Implementation</b> | <b>20</b> |
| <b>2</b> | <b>应用</b>                              | <b>1</b>  | 8.1       | Application Information               | 20        |
| <b>3</b> | <b>说明</b>                              | <b>1</b>  | 8.2       | Typical Applications                  | 22        |
| <b>4</b> | <b>修订历史记录</b>                          | <b>2</b>  | <b>9</b>  | <b>Power Supply Recommendations</b>   | <b>27</b> |
| <b>5</b> | <b>Pin Configuration and Functions</b> | <b>3</b>  | <b>10</b> | <b>Layout</b>                         | <b>28</b> |
| <b>6</b> | <b>Specifications</b>                  | <b>4</b>  | 10.1      | Layout Guidelines                     | 28        |
| 6.1      | Absolute Maximum Ratings               | 4         | 10.2      | Layout Example                        | 29        |
| 6.2      | ESD Ratings                            | 4         | <b>11</b> | <b>器件和文档支持</b>                        | <b>30</b> |
| 6.3      | Recommended Operating Conditions       | 4         | 11.1      | 器件支持                                  | 30        |
| 6.4      | Thermal Information                    | 4         | 11.2      | 文档支持                                  | 30        |
| 6.5      | Electrical Characteristics             | 5         | 11.3      | 接收文档更新通知                              | 30        |
| 6.6      | Typical Characteristics                | 6         | 11.4      | 社区资源                                  | 30        |
| <b>7</b> | <b>Detailed Description</b>            | <b>14</b> | 11.5      | 商标                                    | 31        |
| 7.1      | Overview                               | 14        | 11.6      | 静电放电警告                                | 31        |
| 7.2      | Functional Block Diagram               | 14        | 11.7      | Glossary                              | 31        |
| 7.3      | Feature Description                    | 15        | <b>12</b> | <b>机械、封装和可订购信息</b>                    | <b>31</b> |
| 7.4      | Device Functional Modes                | 19        |           |                                       |           |

---

**4 修订历史记录**

| 日期         | 修订版本 | 说明    |
|------------|------|-------|
| 2019 年 7 月 | *    | 初始发行版 |

## 5 Pin Configuration and Functions



**Pin Functions**

| PIN   |     | I/O | DESCRIPTION                  |
|-------|-----|-----|------------------------------|
| NAME  | NO. |     |                              |
| -IN A | 2   | I   | Inverting input channel A    |
| +IN A | 3   | I   | Noninverting input channel A |
| -IN B | 6   | I   | Inverting input channel B    |
| +IN B | 5   | I   | Noninverting input channel B |
| OUT A | 1   | O   | Output channel A             |
| OUT B | 7   | O   | Output channel B             |
| V-    | 4   | —   | Negative supply              |
| V+    | 8   | —   | Positive supply              |

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

|                                     |                                     |  | MIN          | MAX                 | UNIT |
|-------------------------------------|-------------------------------------|--|--------------|---------------------|------|
| $V_S$                               | Supply voltage, $V_S = (V+) - (V-)$ |  |              | 26                  | V    |
| Input voltage                       | Common-mode                         |  | $(V-) - 0.5$ | $(V+) + 0.5$        | V    |
|                                     | Differential                        |  |              | $(V+) - (V-) + 0.2$ |      |
| Output short-circuit <sup>(2)</sup> |                                     |  | Continuous   |                     |      |
| $T_J$                               | Operating junction temperature      |  | -40          | 150                 | °C   |
| $T_{stg}$                           | Storage temperature                 |  | -65          | 150                 | °C   |

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) Short-circuit to ground, one amplifier per package.

### 6.2 ESD Ratings

|             |                         |  | VALUE | UNIT |
|-------------|-------------------------|--|-------|------|
| $V_{(ESD)}$ | Electrostatic discharge | Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>              | 4000  | V    |
|             |                         | Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup> | 1500  |      |

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

|       |                       |               | MIN | NOM        | MAX      | UNIT |
|-------|-----------------------|---------------|-----|------------|----------|------|
| $V_S$ | Supply Voltage        | Single supply |     | 4.5        | 24       |      |
|       |                       | Dual supply   |     | $\pm 2.25$ | $\pm 12$ | V    |
| $T_A$ | Specified temperature |               | -40 |            | 125      | °C   |

### 6.4 Thermal Information

| THERMAL METRIC <sup>(1)</sup> |  | TLV2186  | UNIT |
|-------------------------------|--|----------|------|
|                               |  | D (SOIC) |      |
|                               |  | 8 PINS   |      |
| $R_{iJA}$                     | Junction-to-ambient thermal resistance       | 129.4    | °C/W |
| $R_{iJC(top)}$                | Junction-to-case (top) thermal resistance    | 69.6     | °C/W |
| $R_{iJB}$                     | Junction-to-board thermal resistance         | 72.8     | °C/W |
| $\Psi_{JT}$                   | Junction-to-top characterization parameter   | 20.8     | °C/W |
| $\Psi_{JB}$                   | Junction-to-board characterization parameter | 72.0     | °C/W |
| $R_{iJC(bot)}$                | Junction-to-case (bottom) thermal resistance | N/A      | °C/W |

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

## 6.5 Electrical Characteristics

at  $T_A = 25^\circ\text{C}$ ,  $V_S = \pm 2.25\text{V}$  to  $\pm 12\text{V}$ ,  $R_L = 10\text{ k}\Omega$  connected to  $V_S / 2$ ,  $V_{CM} = V_S / 2$ , and  $V_{OUT} = V_S / 2$  (unless otherwise noted)

| PARAMETER                 | TEST CONDITIONS                      |  | MIN   | TYP                | MAX       | UNIT                                 |
|---------------------------|--------------------------------------|--|---|--------------------|-----------|--------------------------------------|
| <b>OFFSET VOLTAGE</b>     |                                      |  |   |                    |           |                                      |
| $V_{OS}$                  | Input offset voltage                 |  |   | $\pm 10$           | $\pm 250$ | $\mu\text{V}$                        |
| $dV_{OS}/dT$              | Input offset voltage drift           | $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$  |   | $\pm 0.1$          | $\pm 1.0$ | $\mu\text{V}/^\circ\text{C}$         |
| PSRR                      | Power-supply rejection ratio         | $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$  |   | $\pm 0.05$         | $\pm 1$   | $\mu\text{V}/\text{V}$               |
| <b>INPUT BIAS CURRENT</b> |                                      |  |   |                    |           |                                      |
| $I_B$                     | Input bias current                   |  |   | 0.1                | 0.6       | $\text{nA}$                          |
|                           |                                      | $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$   |   |                    | 0.6       |                                      |
|                           |                                      | $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$  |   |                    | 5         |                                      |
| $I_{OS}$                  | Input offset current                 |  |   | 0.1                | 1.2       | $\text{nA}$                          |
|                           |                                      | $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$   |   |                    | 1.2       |                                      |
|                           |                                      | $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$  |   |                    | 2         |                                      |
| <b>NOISE</b>              |                                      |  |   |                    |           |                                      |
|                           | Input voltage noise                  | $f = 0.1\text{ Hz}$ to $10\text{ Hz}$  |   | 110                |           | $\text{nV}_{\text{RMS}}$             |
| $e_N$                     | Input voltage noise density          | $f = 1\text{ kHz}$   |   | 38                 |           | $\text{nV}/\sqrt{\text{Hz}}$         |
| $i_N$                     | Input current noise                  | $f = 1\text{ kHz}$   |   | 100                |           | $\text{fA}/\sqrt{\text{Hz}}$         |
| <b>INPUT VOLTAGE</b>      |                                      |  |   |                    |           |                                      |
| $V_{CM}$                  | Common-mode voltage                  |  | $(V-) - 0.2$  | $(V+) + 0.2$       |           | $\text{V}$                           |
| CMRR                      | Common-mode rejection ratio          | $(V-) - 0.1 < V_{CM} < (V+) + 0.1\text{ V}$ ,<br>$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$ | $V_S = \pm 2.25\text{ V}$   | 108                | 126       | $\text{dB}$                          |
|                           |                                      |  | $V_S = \pm 12\text{ V}$   | 110                | 134       |                                      |
|                           |                                      | $(V-) - 0.1 < V_{CM} < (V+) + 0.1\text{ V}$ ,<br>$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$ | $V_S = \pm 2.25\text{ V}$   | 106                | 114       |                                      |
|                           |                                      |  | $V_S = \pm 12\text{ V}$   | 106                | 120       |                                      |
| <b>FREQUENCY RESPONSE</b> |                                      |  |   |                    |           |                                      |
| GBW                       | Gain-bandwidth product               |  |   | 750                |           | $\text{kHz}$                         |
| SR                        | Slew rate                            | $1\text{-V step, G} = 1$   |   | 0.35               |           | $\text{V}/\mu\text{s}$               |
| $t_S$                     | Settling time                        | To 0.1%, 1-V step, $G = 1$   |   | 7.5                |           | $\mu\text{s}$                        |
|                           | Overload recovery time               | $V_{IN} \times \text{gain} > V_S$  |   | 10                 |           | $\mu\text{s}$                        |
| <b>INPUT CAPACITANCE</b>  |                                      |  |   |                    |           |                                      |
| $Z_{ID}$                  | Differential                         |  |   | 100 $\parallel$ 5  |           | $\text{M}\Omega \parallel \text{pF}$ |
| $Z_{ICM}$                 | Common-mode                          |  |   | 50 $\parallel$ 2.5 |           | $\text{G}\Omega \parallel \text{pF}$ |
| <b>OPEN-LOOP GAIN</b>     |                                      |  |   |                    |           |                                      |
| $A_{OL}$                  | Open-loop voltage gain               | $V_S = \pm 12\text{ V}$  | $(V-) + 0.3\text{ V} < V_O < (V+) - 0.3\text{ V}$ , $R_L = 10\text{ k}\Omega$   | 120                | 140       | $\text{dB}$                          |
|                           |                                      |  | $(V-) + 0.3\text{ V} < V_O < (V+) - 0.3\text{ V}$ , $R_L = 10\text{ k}\Omega$ , $T_A = -40^\circ\text{C}$ to $125^\circ\text{C}$  | 120                | 134       |                                      |
|                           |                                      |  | $(V-) + 0.65\text{ V} < V_O < (V+) - 0.65\text{ V}$ , $R_L = 2\text{ k}\Omega$  | 120                | 140       |                                      |
|                           |                                      |  | $(V-) + 0.65\text{ V} < V_O < (V+) - 0.65\text{ V}$ , $R_L = 2\text{ k}\Omega$ , $T_A = -40^\circ\text{C}$ to $125^\circ\text{C}$ | 120                | 134       |                                      |
| <b>OUTPUT</b>             |                                      |  |   |                    |           |                                      |
| $V_O$                     | Voltage output swing from both rails |  | No load   | 5                  | 20        | $\text{mV}$                          |
|                           |                                      |  | $R_L = 10\text{ k}\Omega$   | 60                 | 100       |                                      |
|                           |                                      |  | $R_L = 2\text{ k}\Omega$  | 340                | 500       |                                      |
|                           |                                      |  | $R_L = 10\text{ k}\Omega$ , $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$   | 90                 | 115       |                                      |
| $I_{SC}$                  | Short-circuit current                |  |   | $\pm 20$           |           | $\text{mA}$                          |
| $C_{LOAD}$                | Capacitive load drive                |  |   | See typical curves |           |                                      |
| $R_O$                     | Open-loop output impedance           |  |   | See typical curves |           |                                      |
| <b>POWER SUPPLY</b>       |                                      |  |   |                    |           |                                      |
| $I_Q$                     | Quiescent current per amplifier      | $V_S = \pm 2.25$ to $\pm 12\text{ V}$  | $T_A = -40^\circ\text{C}$ to $125^\circ\text{C}$  | 90                 | 130       | $\mu\text{A}$                        |
|                           |                                      |  |   |                    | 150       |                                      |

## 6.6 Typical Characteristics

表 1. Typical Characteristic Graphs

| DESCRIPTION   | FIGURE |
|---|--------|
| Offset Voltage Distribution                                       | 图 1    |
| Offset Voltage Drift (-40°C to +125°C)                            | 图 2    |
| Input Bias Current Distribution                                   | 图 3    |
| Input Offset Current Distribution                                 | 图 4    |
| Offset Voltage vs Common-Mode Voltage                             | 图 5    |
| Offset Voltage vs Supply Voltage                                  | 图 6    |
| Open-Loop Gain and Phase vs Frequency                             | 图 7    |
| Closed-Loop Gain vs Frequency                                     | 图 8    |
| Input Bias Current and Offset Current vs Temperature              | 图 9    |
| Output Voltage Swing vs Output Current (Sourcing)                 | 图 10   |
| Output Voltage Swing vs Output Current (Sinking)                  | 图 11   |
| CMRR and PSRR vs Frequency  | 图 12   |
| CMRR vs Temperature   | 图 13   |
| PSRR vs Temperature   | 图 14   |
| 0.1-Hz to 10-Hz Voltage Noise                                     | 图 15   |
| Input Voltage Noise Spectral Density vs Frequency                 | 图 16   |
| THD+N vs Frequency  | 图 17   |
| THD+N vs Output Amplitude   | 图 18   |
| Quiescent Current vs Supply Voltage                               | 图 19   |
| Quiescent Current vs Temperature                                  | 图 20   |
| Open-Loop Gain vs Temperature (10 kΩ)                             | 图 21   |
| Open-Loop Gain vs Temperature (2 kΩ)                              | 图 22   |
| Open-Loop Output Impedance vs Frequency                           | 图 23   |
| Small-Signal Overshoot vs Capacitive Load (Gain = -1, 10-mV step) | 图 24   |
| Small-Signal Overshoot vs Capacitive Load (Gain = 1, 10-mV step)  | 图 25   |
| No Phase Reversal   | 图 26   |
| Positive Overload Recovery  | 图 27   |
| Negative Overload Recovery  | 图 28   |
| Small-Signal Step Response (Gain = 1, 10-mV step)                 | 图 29   |
| Small-Signal Step Response (Gain = -1, 10-mV step)                | 图 30   |
| Large-Signal Step Response (Gain = 1, 10-V step)                  | 图 31   |
| Large-Signal Step Response (Gain = -1, 10-V step)                 | 图 32   |
| Phase Margin vs Capacitive Load                                   | 图 33   |
| Settling Time (1-V Step, 0.1% Settling)                           | 图 34   |
| Short Circuit Current vs Temperature                              | 图 35   |
| Maximum Output Voltage vs Frequency                               | 图 36   |
| EMIRR vs Frequency  | 图 37   |
| Channel Separation  | 图 38   |

at  $T_A = 25^\circ\text{C}$ ,  $V_S = \pm 12\text{ V}$ ,  $V_{CM} = V_S / 2$ ,  $R_L = 10\text{ k}\Omega$  (unless otherwise noted)

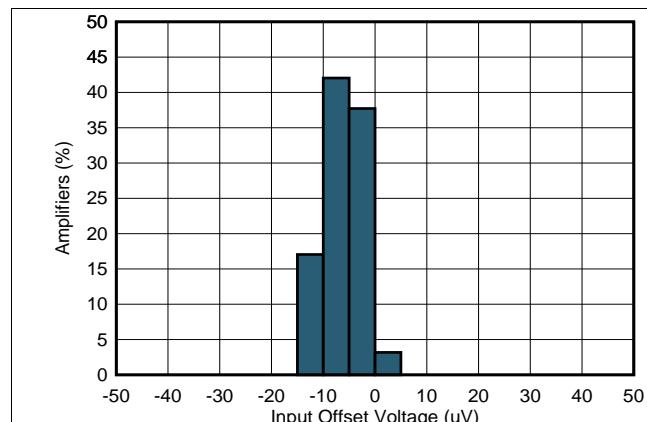


图 1. Offset Voltage Distribution

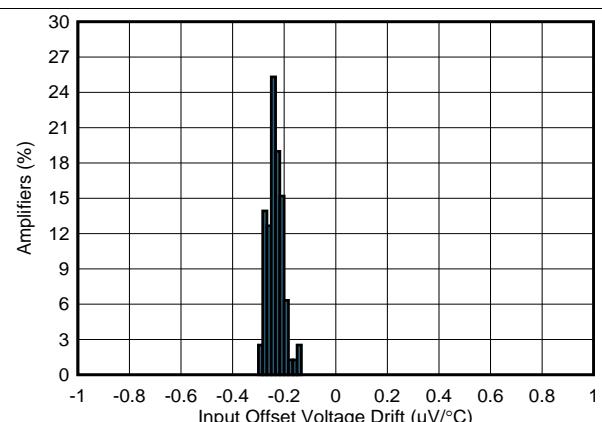


图 2. Offset Voltage Drift (-40°C to 125°C)

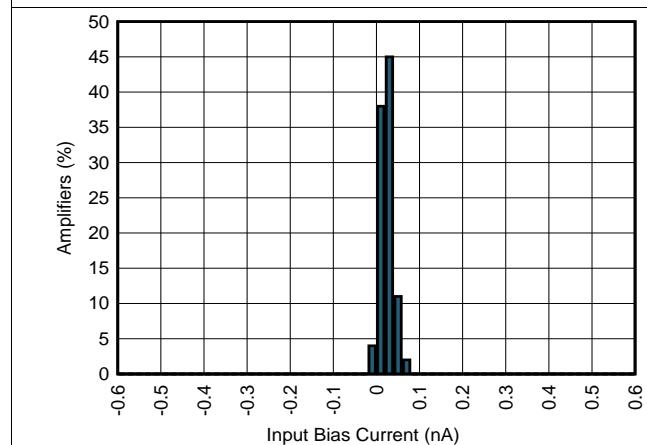


图 3. Input Bias Current Distribution

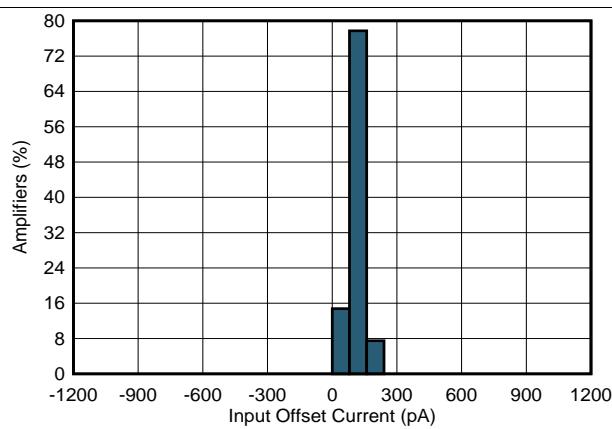


图 4. Input Offset Current Distribution

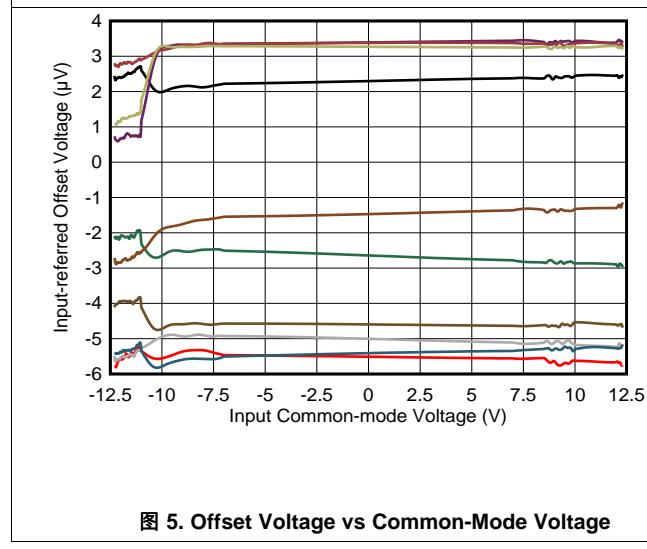


图 5. Offset Voltage vs Common-Mode Voltage

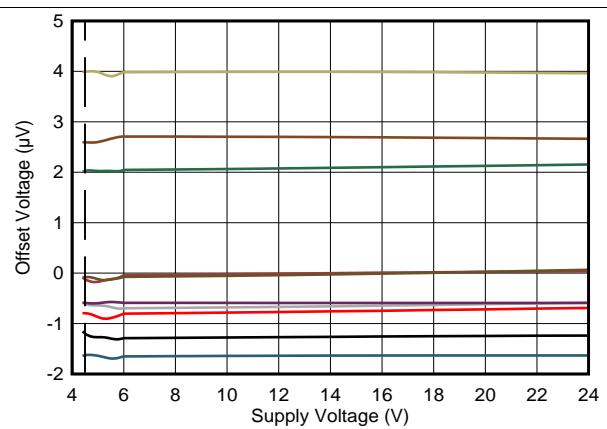


图 6. Offset Voltage vs Supply Voltage

at  $T_A = 25^\circ\text{C}$ ,  $V_S = \pm 12\text{ V}$ ,  $V_{CM} = V_S / 2$ ,  $R_L = 10\text{ k}\Omega$  (unless otherwise noted)

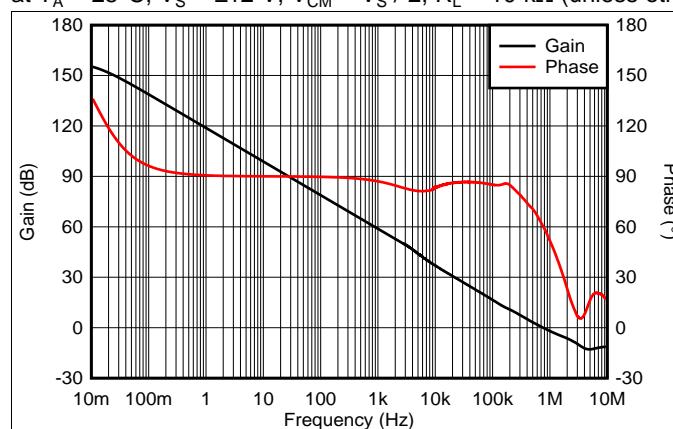


图 7. Open-Loop Gain and Phase vs Frequency

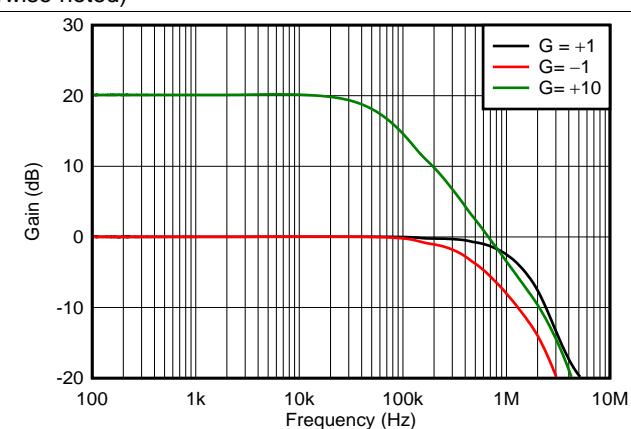


图 8. Closed-Loop Gain vs Frequency

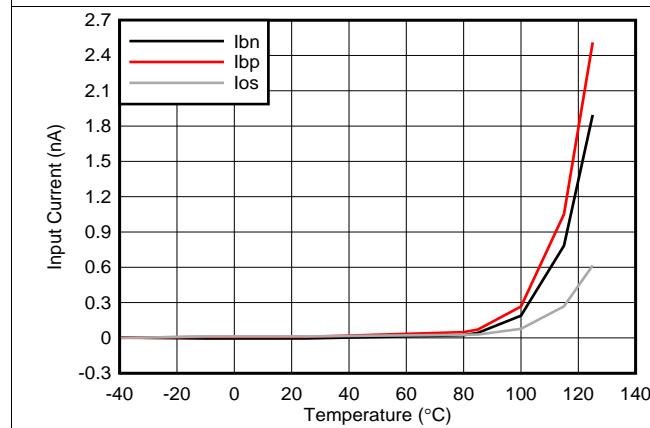


图 9. Input Bias Current and Offset Current vs Temperature

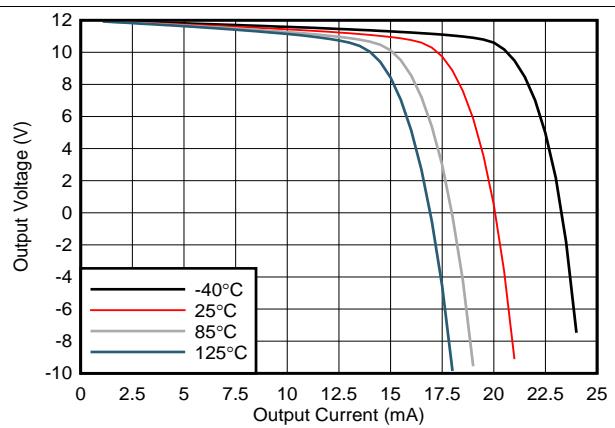


图 10. Output Voltage Swing vs Output Current (Sourcing)

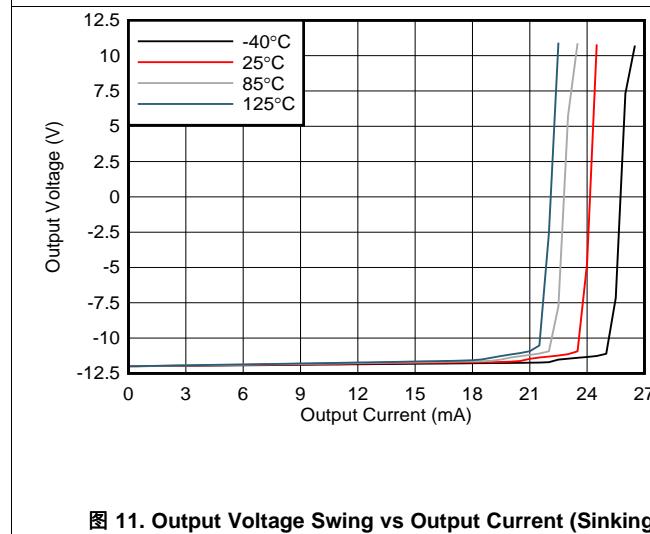


图 11. Output Voltage Swing vs Output Current (Sinking)

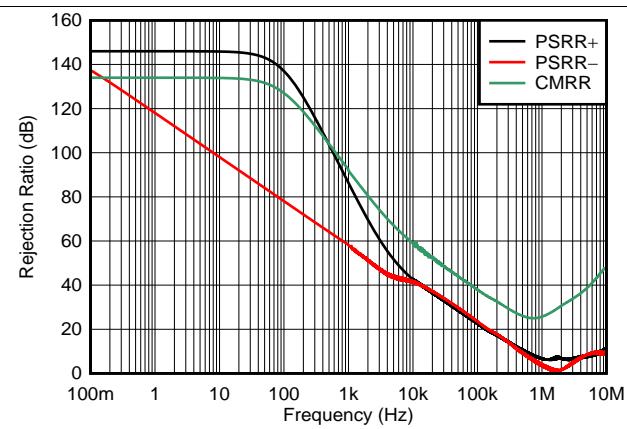


图 12. CMRR and PSRR vs Frequency

at  $T_A = 25^\circ\text{C}$ ,  $V_S = \pm 12\text{ V}$ ,  $V_{\text{CM}} = V_S / 2$ ,  $R_L = 10\text{ k}\Omega$  (unless otherwise noted)

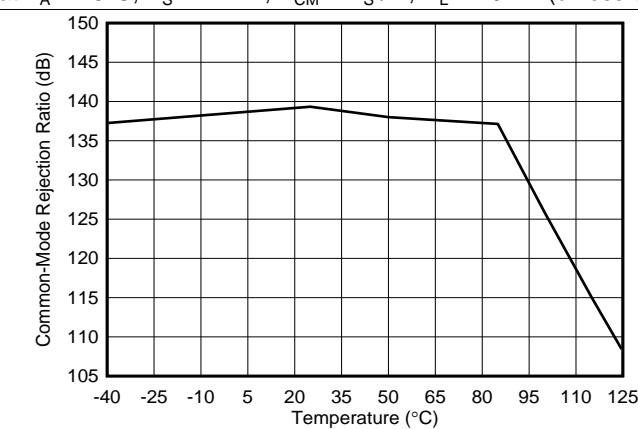


图 13. CMRR vs Temperature

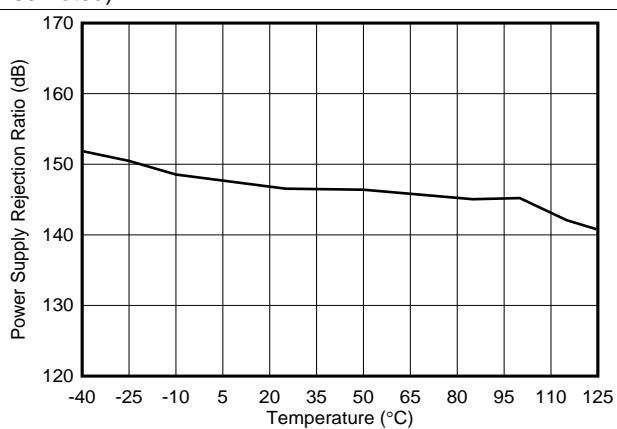


图 14. PSRR vs Temperature

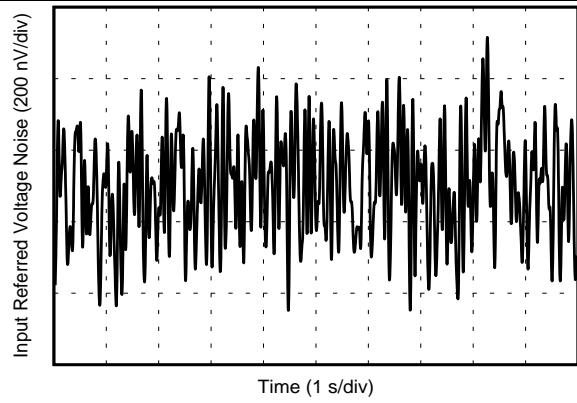


图 15. 0.1-Hz to 10-Hz Voltage Noise

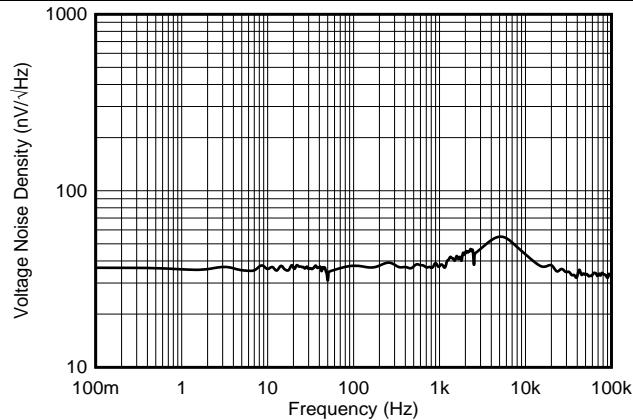


图 16. Input Voltage Noise Spectral Density vs Frequency

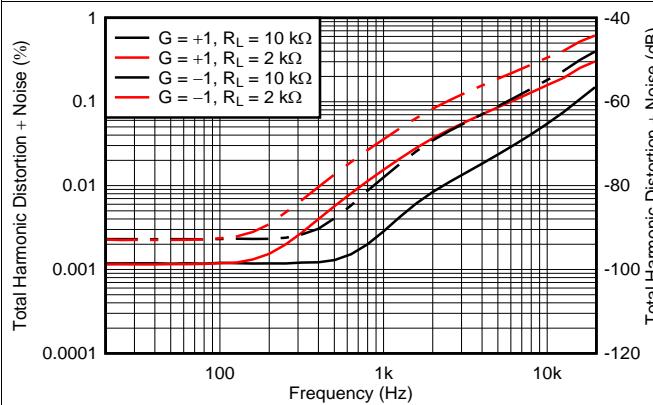


图 17. THD+N vs Frequency

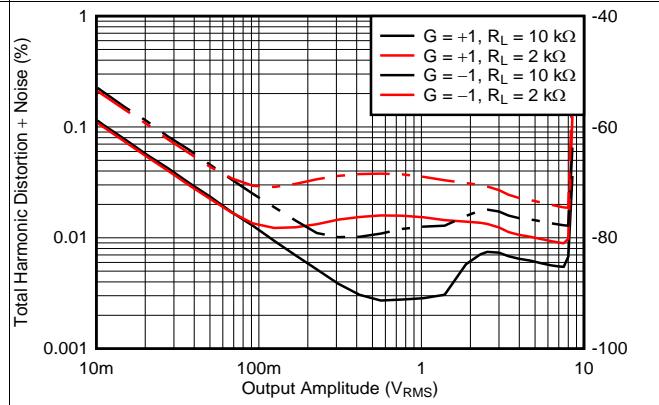


图 18. THD+N vs Output Amplitude

at  $T_A = 25^\circ\text{C}$ ,  $V_S = \pm 12\text{ V}$ ,  $V_{CM} = V_S / 2$ ,  $R_L = 10\text{ k}\Omega$  (unless otherwise noted)

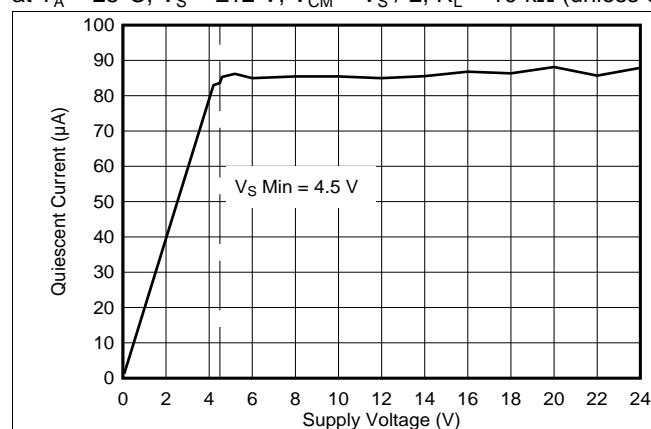


图 19. Quiescent Current vs Supply Voltage

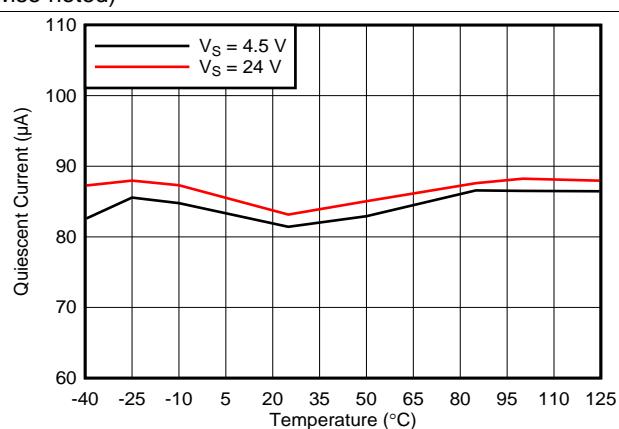


图 20. Quiescent Current vs Temperature

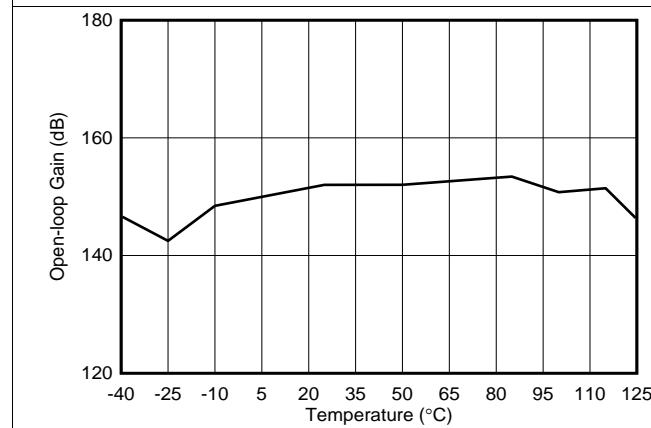


图 21. Open-Loop Gain vs Temperature

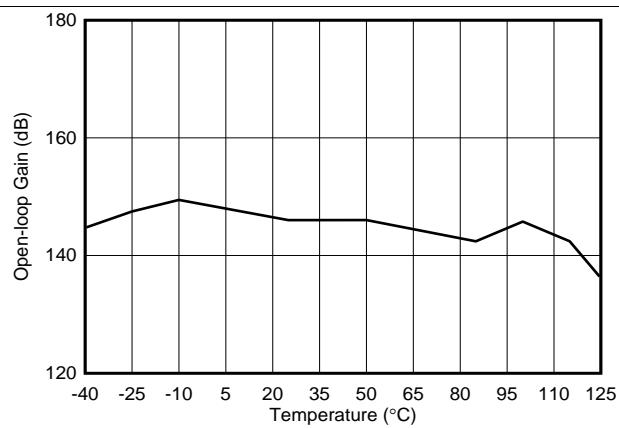


图 22. Open-Loop Gain vs Temperature

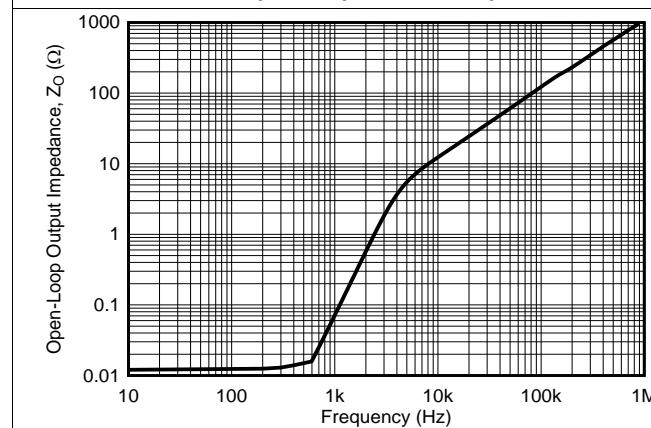


图 23. Open-Loop Output Impedance vs Frequency

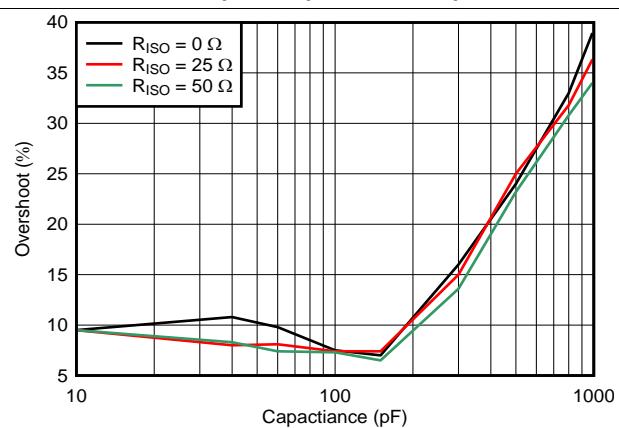
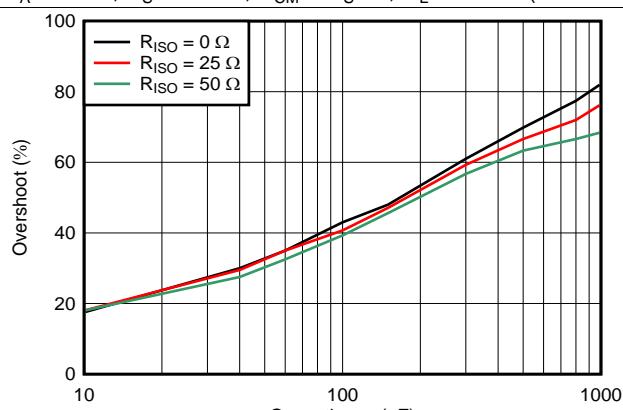


图 24. Small-Signal Overshoot vs Capacitive Load

at  $T_A = 25^\circ\text{C}$ ,  $V_S = \pm 12\text{ V}$ ,  $V_{CM} = V_S / 2$ ,  $R_L = 10\text{ k}\Omega$  (unless otherwise noted)



Gain = 1, 10-mV step

图 25. Small-Signal Overshoot vs Capacitive Load

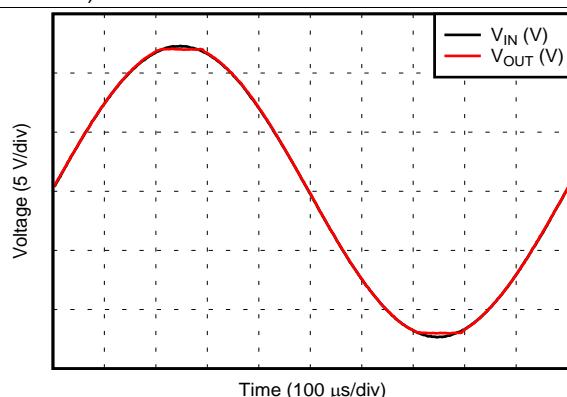


图 26. No Phase Reversal

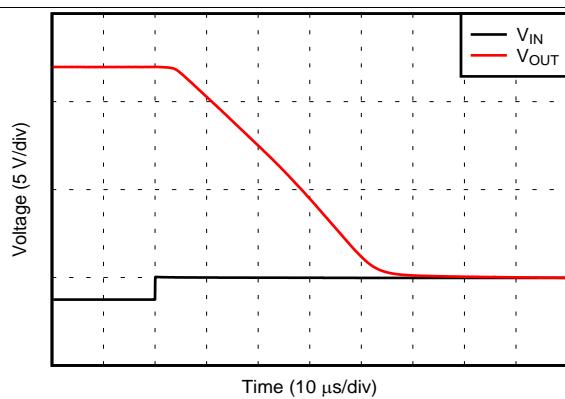


图 27. Positive Overload Recovery

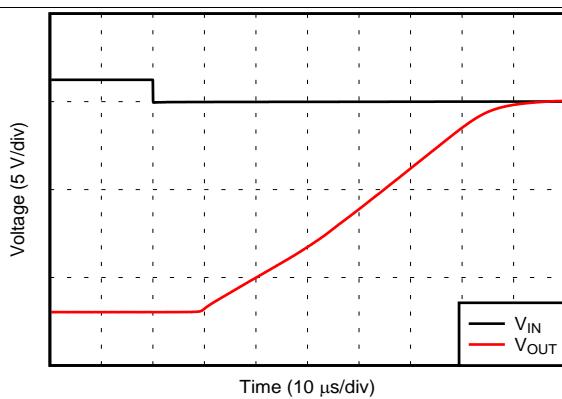
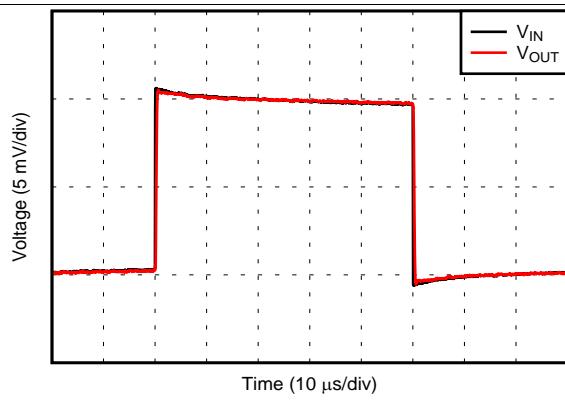
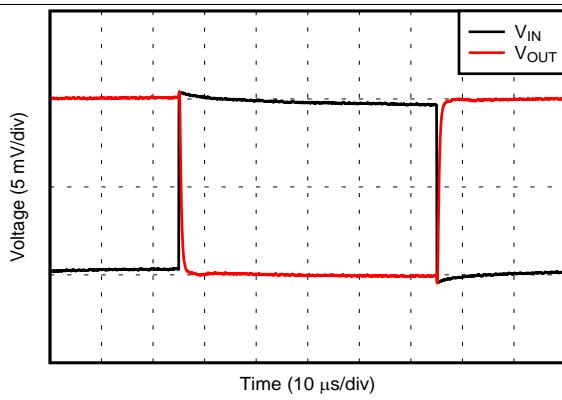


图 28. Negative Overload Recovery



Gain = 1, 10-mV step

图 29. Small-Signal Step Response



Gain = -1, 10-mV step

图 30. Small-Signal Step Response

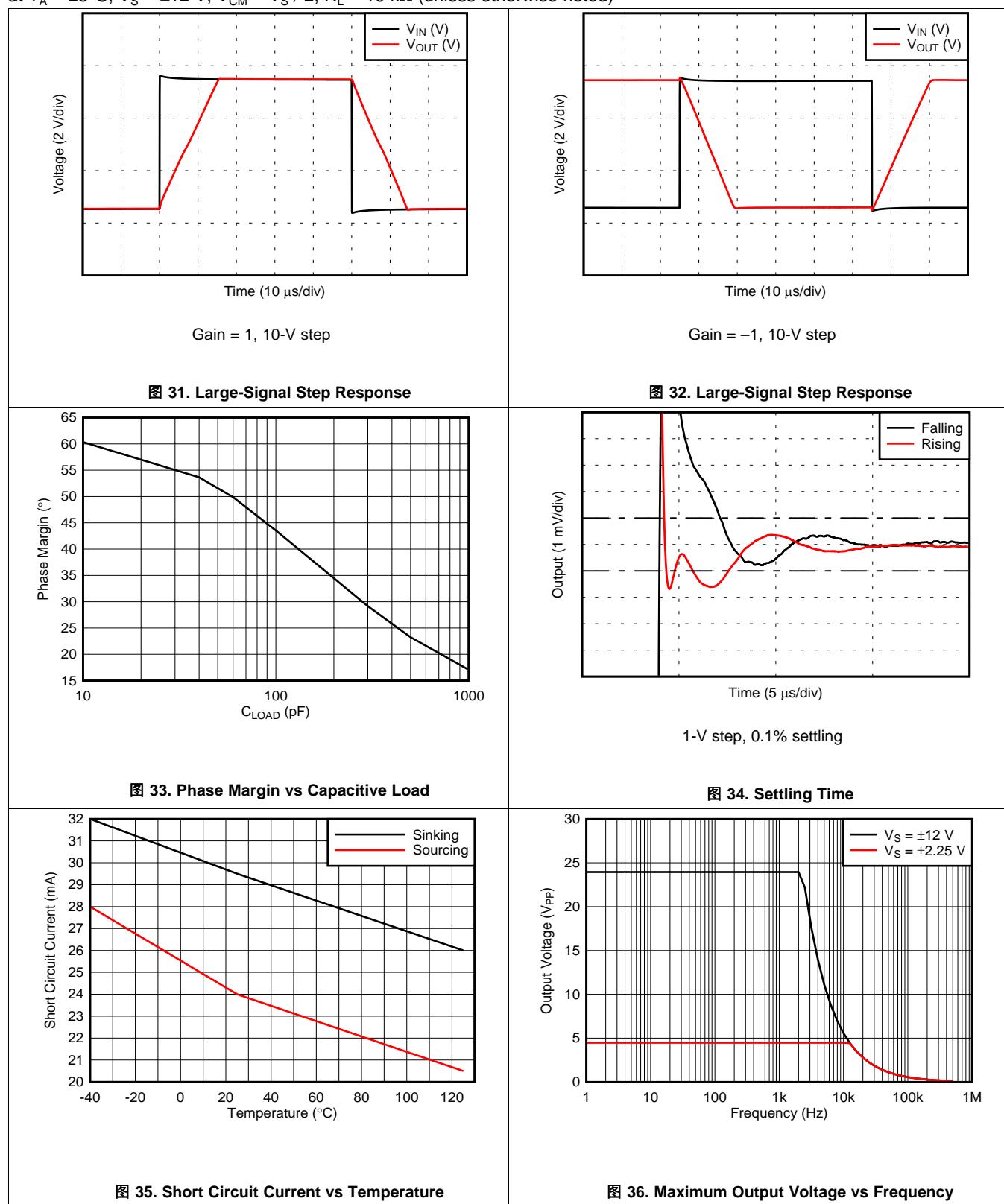
at  $T_A = 25^\circ\text{C}$ ,  $V_S = \pm 12\text{ V}$ ,  $V_{CM} = V_S / 2$ ,  $R_L = 10\text{ k}\Omega$  (unless otherwise noted)


图 31. Large-Signal Step Response

图 32. Large-Signal Step Response

图 33. Phase Margin vs Capacitive Load

图 34. Settling Time

图 35. Short Circuit Current vs Temperature

图 36. Maximum Output Voltage vs Frequency

at  $T_A = 25^\circ\text{C}$ ,  $V_S = \pm 12\text{ V}$ ,  $V_{CM} = V_S / 2$ ,  $R_L = 10\text{ k}\Omega$  (unless otherwise noted)

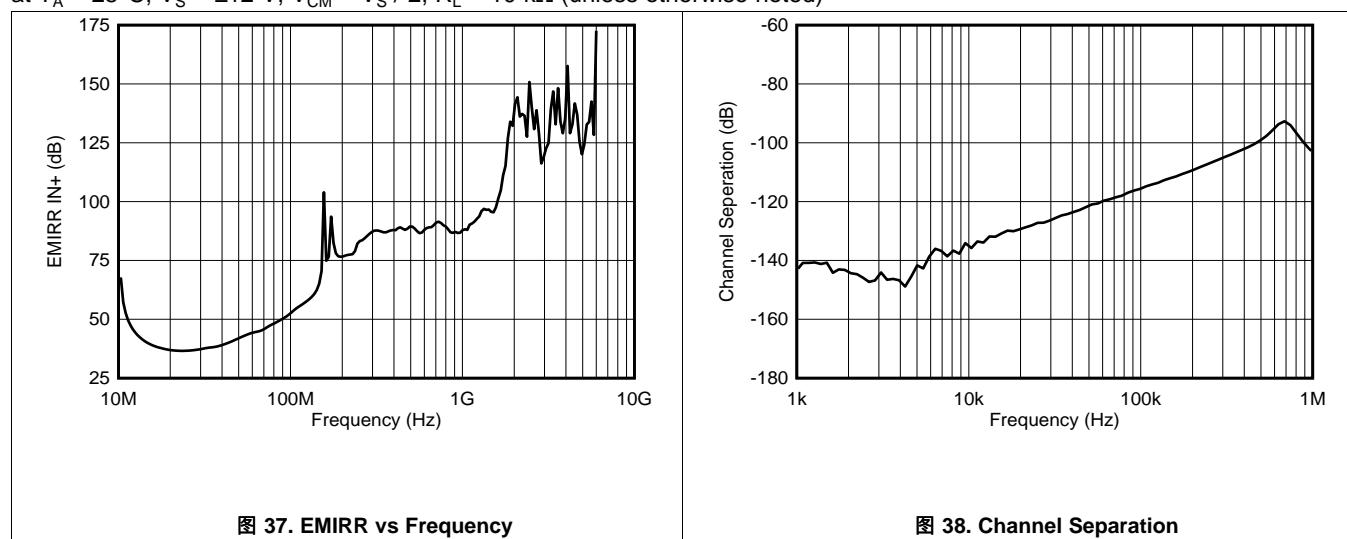


图 37. EMIRR vs Frequency

图 38. Channel Separation

## 7 Detailed Description

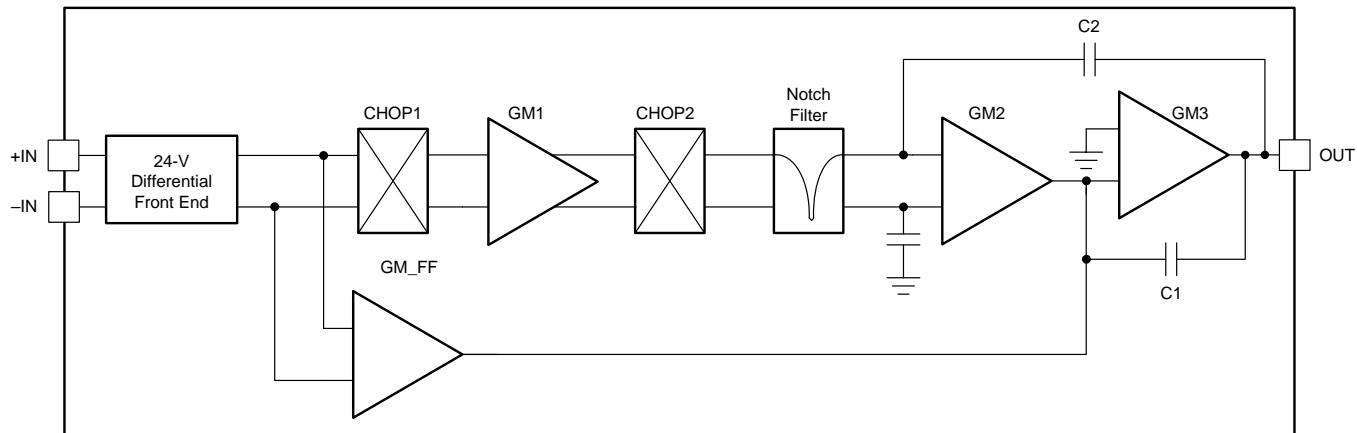
### 7.1 Overview

The TLV2186 operational amplifier combines precision offset and drift with excellent overall performance, making the device a great choice for a wide variety of precision applications. The precision offset drift of only  $0.1 \mu\text{V}/^\circ\text{C}$  provides stability over the entire operating temperature range of  $-40^\circ\text{C}$  to  $+125^\circ\text{C}$ . In addition, this device offers excellent linear performance with high CMRR, PSRR, and  $A_{OL}$ . As with all amplifiers, applications with noisy or high-impedance power supplies require decoupling capacitors close to the device pins. In most cases,  $0.1\text{-}\mu\text{F}$  capacitors are adequate. See the [Layout Guidelines](#) section for details and a layout example.

The TLV2186 is part of a family of zero-drift, MUX-friendly, rail-to-rail output operational amplifiers. This device operates from 4.5 V to 24 V, is unity-gain stable, and is designed for a wide range of general-purpose and precision applications. The zero-drift architecture provides ultra-low input offset voltage and near-zero input offset voltage drift over temperature and time. This choice of architecture also offers outstanding ac performance, such as ultra-low broadband noise, zero flicker noise, and outstanding distortion performance when operating below the chopper frequency.

### 7.2 Functional Block Diagram

The [Functional Block Diagram](#) shows a representation of the proprietary TLV2186 architecture.



## 7.3 Feature Description

The TLV2186 operational amplifier has several integrated features to help maintain a high level of precision through a variety of applications. These include a rail-to-rail inputs, phase-reversal protection, input bias current clock feedthrough, EMI rejection, electrical overstress protection and MUX-friendly Inputs.

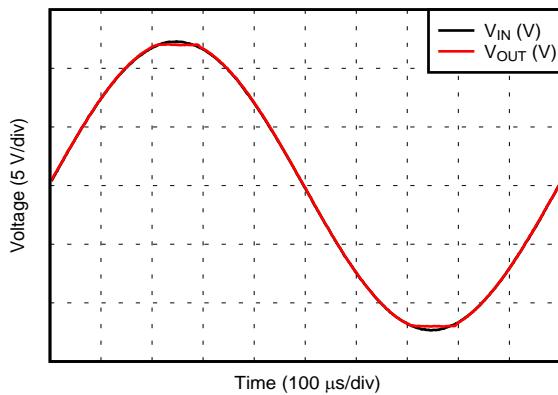
### 7.3.1 Rail-to-Rail Inputs

Unlike many chopper amplifiers, the TLV2186 has rail-to-rail inputs that allow the input common-mode voltage to not only reach, but exceed the supply voltages by 200 mV. This configuration simplifies power-supply requirements by not requiring headroom over the input signal range.

The TLV2186 is specified for operation from 4.5 V to 24 V ( $\pm 2.25$  V to  $\pm 12$  V) with rail-to-rail inputs. Many specifications apply from  $-40^\circ\text{C}$  to  $+125^\circ\text{C}$ . Parameters that can exhibit significant variance with regard to operating voltage or temperature are presented in the *Typical Characteristics* section.

### 7.3.2 Phase-Reversal Protection

The TLV2186 has internal phase-reversal protection. Some op amps exhibit a phase reversal when the input is driven beyond the linear common-mode range. This condition is most often encountered in noninverting circuits when the input is driven beyond the specified common-mode voltage range, causing the output to reverse into the opposite rail. The TLV2186 input prevents phase reversal with excessive common-mode voltage. Instead, the output limits into the appropriate rail. This performance is shown in [图 39](#).



**图 39. No Phase Reversal**

### 7.3.3 Input Bias Current Clock Feedthrough

Zero-drift amplifiers such as the TLV2186 use a switching architecture on the inputs to correct for the intrinsic offset and drift of the amplifier. Charge injection from the integrated switches on the inputs can introduce short transients in the input bias current of the amplifier. The extremely short duration of these pulses prevents the pulses from amplifying, however the pulses may be coupled to the output of the amplifier through the feedback network. The most effective method to prevent transients in the input bias current from producing additional noise at the amplifier output is to use a low-pass filter, such as an RC network.

## Feature Description (接下页)

### 7.3.4 EMI Rejection

The TLV2186 uses integrated electromagnetic interference (EMI) filtering to reduce the effects of EMI interference from sources such as wireless communications and densely-populated boards with a mix of analog signal chain and digital components. EMI immunity can be improved with circuit design techniques; the TLV2186 benefits from these design improvements. Texas Instruments has developed the ability to accurately measure and quantify the immunity of an operational amplifier over a broad frequency spectrum extending from 10 MHz to 6 GHz. [图 40](#) shows the results of this testing on the TLV2186. [表 2](#) lists the EMIRR  $+IN$  values for the TLV2186 at particular frequencies commonly encountered in real-world applications. Applications listed in [表 2](#) may be centered on or operated near the particular frequency shown. Detailed information can also be found in the [EMI Rejection Ratio of Operational Amplifiers](#) (SBOA128), available for download from [www.ti.com](#).

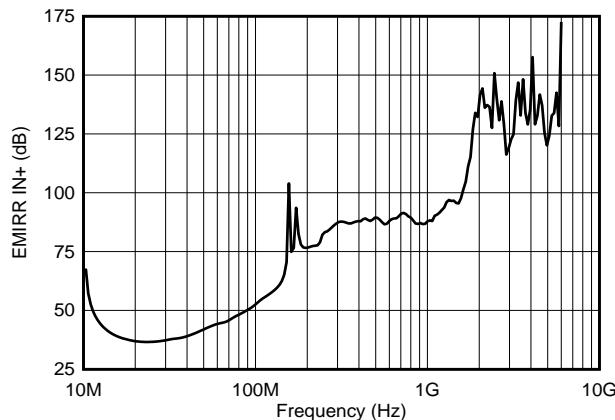


图 40. EMIRR Testing

表 2. TLV2186 EMIRR IN+ for Frequencies of Interest

| FREQUENCY | APPLICATION AND ALLOCATION   | EMIRR IN+ |
|-----------|--|-----------|
| 400 MHz   | Mobile radio, mobile satellite, space operation, weather, radar, ultra-high frequency (UHF) applications   | 48.4 dB   |
| 900 MHz   | Global system for mobile communications (GSM) applications, radio communication, navigation, GPS (to 1.6 GHz), GSM, aeronautical mobile, UHF applications                        | 52.8 dB   |
| 1.8 GHz   | GSM applications, mobile personal communications, broadband, satellite, L-band (1 GHz to 2 GHz)  | 69.1 dB   |
| 2.4 GHz   | 802.11b, 802.11g, 802.11n, Bluetooth®, mobile personal communications, industrial, scientific and medical (ISM) radio band, amateur radio and satellite, S-band (2 GHz to 4 GHz) | 88.9 dB   |
| 3.6 GHz   | Radiolocation, aero communication and navigation, satellite, mobile, S-band  | 82.5 dB   |
| 5 GHz     | 802.11a, 802.11n, aero communication and navigation, mobile communication, space and satellite operation, C-band (4 GHz to 8 GHz)  | 95.5 dB   |

The electromagnetic interference (EMI) rejection ratio, or EMIRR, describes the EMI immunity of operational amplifiers. An adverse effect that is common to many op amps is a change in the offset voltage as a result of RF signal rectification. An op amp that is more efficient at rejecting this change in offset as a result of EMI has a higher EMIRR and is quantified by a decibel value. Measuring EMIRR can be performed in many ways, but this section provides the EMIRR +IN, which specifically describes the EMIRR performance when the RF signal is applied to the noninverting input pin of the op amp. In general, only the noninverting input is tested for EMIRR for the following three reasons:

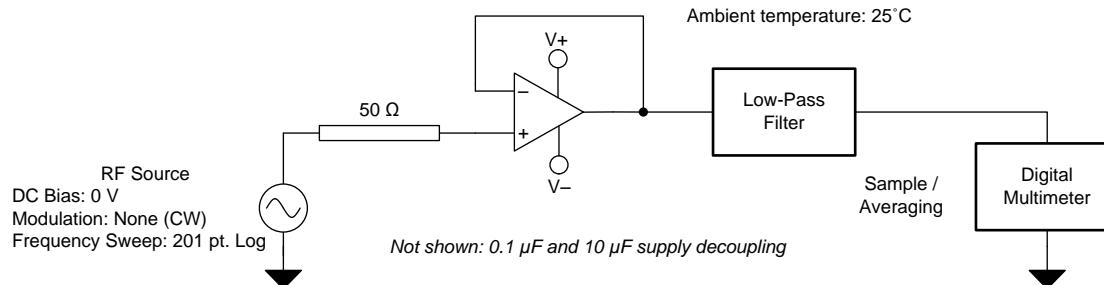
- Op amp input pins are known to be the most sensitive to EMI, and typically rectify RF signals better than the supply or output pins.
- The noninverting and inverting op amp inputs have symmetrical physical layouts and exhibit nearly matching EMIRR performance
- EMIRR is more simple to measure on noninverting pins than on other pins because the noninverting input terminal can be isolated on a PCB. This isolation allows the RF signal to be applied directly to the noninverting input terminal with no complex interactions from other components or connecting PCB traces.

High-frequency signals conducted or radiated to any pin of the operational amplifier may result in adverse effects, as the amplifier would not have sufficient loop gain to correct for signals with spectral content outside the bandwidth. Conducted or radiated EMI on inputs, power supply, or output may result in unexpected dc offsets, transient voltages, or other unknown behavior. Take care to properly shield and isolate sensitive analog nodes from noisy radio signals and digital clocks and interfaces.

The EMIRR +IN of the TLV2186 is plotted versus frequency as shown in [图 40](#). The TLV2186 unity-gain bandwidth is 750 kHz. EMIRR performance below this frequency denotes interfering signals that fall within the op amp bandwidth.

#### 7.3.4.1 EMIRR +IN Test Configuration

[图 41](#) shows the circuit configuration for testing the EMIRR +IN. An RF source is connected to the op amp noninverting input terminal using a transmission line. The op amp is configured in a unity-gain buffer topology with the output connected to a low-pass filter (LPF) and a digital multimeter (DMM). A large impedance mismatch at the op amp input causes a voltage reflection; however, this effect is characterized and accounted for when determining the EMIRR IN+. The multimeter samples and measures the resulting DC offset voltage. The LPF isolates the multimeter from residual RF signals that may interfere with multimeter accuracy.



**图 41. EMIRR +IN Test Configuration**

### 7.3.5 Electrical Overstress

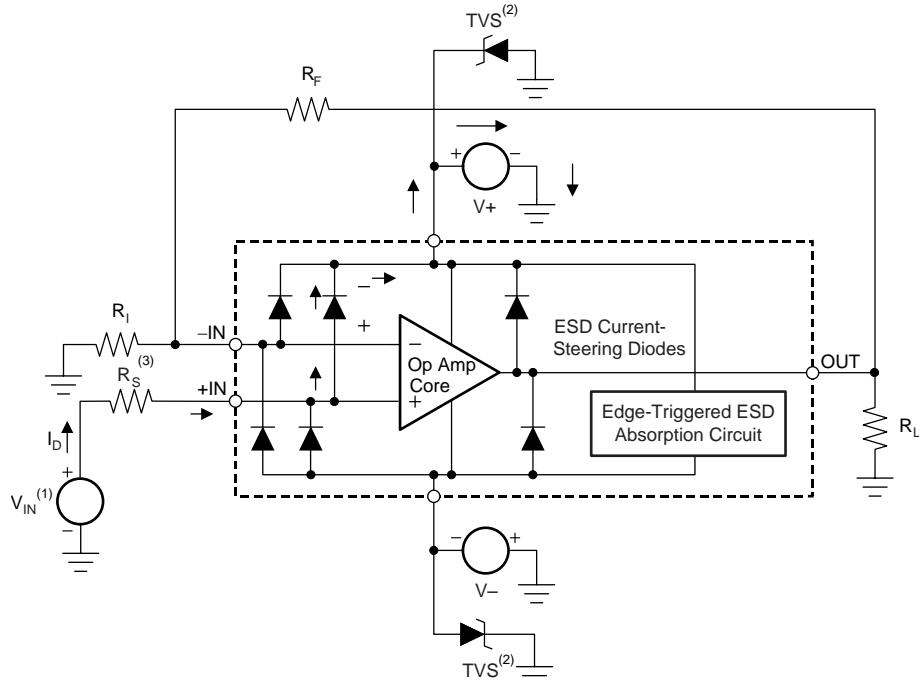
Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress. These questions tend to focus on the device inputs, but may involve the supply voltage pins or even the output pin. Each of these different pin functions have electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits to protect from accidental ESD events both before and during product assembly.

Having a good understanding of this basic ESD circuitry and the relevance to an electrical overstress event is helpful. See [图 42](#) for an illustration of the ESD circuits contained in the TLV2186 (indicated by the dashed line area). The ESD protection circuitry involves several current-steering diodes connected from the input and output pins and routed back to the internal power-supply lines, where the diodes meet at an absorption device internal to the operational amplifier. This protection circuitry is intended to remain inactive during normal circuit operation.

An ESD event produces a short-duration, high-voltage pulse that is transformed into a short-duration, high-current pulse while discharging through a semiconductor device. The ESD protection circuits are designed to provide a current path around the operational amplifier core to prevent damage. The energy absorbed by the protection circuitry is then dissipated as heat.

When an ESD voltage develops across two or more amplifier device pins, current flows through one or more steering diodes. Depending on the path that the current takes, the absorption device may activate. The absorption device has a trigger or threshold voltage that is greater than the normal operating voltage of the TLV2186, but less than the device breakdown voltage level. When this threshold is exceeded, the absorption device quickly activates and clamps the voltage across the supply rails to a safe level.

When the operational amplifier connects into a circuit, as shown in [图 42](#), the ESD protection components are intended to remain inactive, and do not become involved in the application circuit operation. However, circumstances may arise where an applied voltage exceeds the operating voltage range of a given pin. If this condition occurs, there is a risk that some internal ESD protection circuits may be biased on, and conduct current. Any such current flow occurs through steering-diode paths and rarely involves the absorption device.



(1)  $V_{IN} = (V+) + 500 \text{ mV}$

(2) TVS:  $26 \text{ V} > V_{TVSBR \text{ (min)}} > V+$ ; where  $V_{TVSBR \text{ (min)}}$  is the minimum specified value for the transient voltage suppressor breakdown voltage.

(3) Suggested value is approximately  $5 \text{ k}\Omega$  in example overvoltage condition.

**图 42. Equivalent Internal ESD Circuitry Relative to a Typical Circuit Application**

图 42 shows a specific example where the input voltage ( $V_{IN}$ ) exceeds the positive supply voltage ( $V+$ ) by 500 mV or more. Much of what happens in the circuit depends on the supply characteristics. If  $V+$  can sink the current, one of the upper input steering diodes conducts and directs current to  $+V_S$ . Excessively high current levels can flow with increasingly higher  $V_{IN}$ . As a result, the data sheet specifications recommend that applications limit the input current to 10 mA.

If the supply is not capable of sinking the current,  $V_{IN}$  may begin sourcing current to the operational amplifier, and then take over as the source of positive supply voltage. The danger in this case is that the voltage can rise to levels that exceed the operational amplifier absolute maximum ratings.

Another common question involves what happens to the amplifier if an input signal is applied to the input while the power supplies  $V+$  or  $V-$  are at 0 V. Again, this question depends on the supply characteristic while at 0 V, or at a level below the input signal amplitude. If the supplies appear as high impedance, then the operational amplifier supply current may be supplied by the input source through the current-steering diodes. This state is not a normal bias condition; the amplifier most likely does not operate normally. If the supplies are low impedance, then the current through the steering diodes can become quite high. The current level depends on the ability of the input source to deliver current, and any resistance in the input path.

If there is any uncertainty about the ability of the supply to absorb this current, external zener diodes must be added to the supply pins, as shown in 图 42. The zener voltage must be selected such that the diode does not turn on during normal operation. However, the zener voltage must be low enough so that the zener diode conducts if the supply pin begins to rise above the safe operating supply voltage level.

### 7.3.6 MUX-Friendly Inputs

The TLV2186 features a proprietary input stage design that allows an input differential voltage to be applied while maintaining high input impedance. Typically, high-voltage CMOS or bipolar-junction input amplifiers feature antiparallel diodes that protect input transistors from large  $V_{GS}$  voltages that may exceed the semiconductor process maximum and permanently damage the device. Large  $V_{GS}$  voltages can be forced when applying a large input step, switching between channels, or attempting to use the amplifier as a comparator.

The TLV2186 solves these problems with a switched-input technique that prevents large input bias currents when large differential voltages are applied. This solves many issues seen in switched or multiplexed applications, where large disruptions to RC filtering networks are caused by fast switching between large potentials. The TLV2186 offers outstanding settling performance as a result of these design innovations and built-in slew rate boost and wide bandwidth. The TLV2186 can also be used as a comparator. Differential and common-mode *Absolute Maximum Ratings* still apply relative to the power supplies.

## 7.4 Device Functional Modes

The TLV2186 has a single functional mode, and is operational when the power-supply voltage is greater than 4.5 V ( $\pm 2.25$  V). The maximum power supply voltage for the TLV2186 is 24 V ( $\pm 12$  V).

## 8 Application and Implementation

### 注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

The TLV2186 operational amplifier combines precision offset and drift with excellent overall performance, making the device ideal for many precision applications. The precision offset drift of only  $0.1 \mu\text{V}/^\circ\text{C}$  provides stability over the entire temperature range. In addition, the device pairs excellent CMRR, PSRR, and  $A_{OL}$  dc performance with outstanding low-noise operation. As with all amplifiers, applications with noisy or high-impedance power supplies require decoupling capacitors close to the device pins. In most cases,  $0.1\text{-}\mu\text{F}$  capacitors are adequate.

The following application examples highlight only a few of the circuits where the TLV2186 can be used.

#### 8.1.1 Basic Noise Calculations

Low-noise circuit design requires careful analysis of all noise sources. External noise sources can dominate in many cases; consider the effect of source resistance on overall op amp noise performance. Total noise of the circuit is the root-sum-square combination of all noise components.

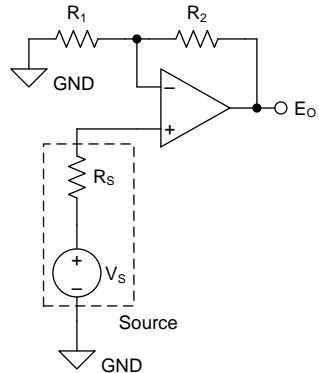
The resistive portion of the source impedance produces thermal noise proportional to the square root of the resistance. The source impedance is usually fixed; consequently, select the op amp and the feedback resistors to minimize the respective contributions to the total noise.

图 43 illustrates both noninverting (**A**) and inverting (**B**) op amp circuit configurations with gain. In circuit configurations with gain, the feedback network resistors also contribute noise. In general, the current noise of the op amp reacts with the feedback resistors to create additional noise components. However, the extremely low current noise of the TLV2186 means that the current noise contribution can be neglected.

The feedback resistor values can generally be chosen to make these noise sources negligible. Low impedance feedback resistors load the output of the amplifier. The equations for total noise are shown for both configurations.

## Application Information (接下页)

### (A) Noise in Noninverting Gain Configuration



Noise at the output is given as  $E_O$ , where

$$(1) \quad E_O = \left(1 + \frac{R_2}{R_1}\right) \cdot \sqrt{(e_S)^2 + (e_N)^2 + (e_{R_1 \parallel R_2})^2 + (i_N \cdot R_S)^2 + \left(i_N \cdot \left[\frac{R_1 \cdot R_2}{R_1 + R_2}\right]\right)^2} \quad [V_{RMS}]$$

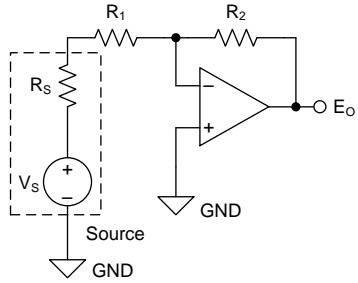
$$(2) \quad e_S = \sqrt{4 \cdot k_B \cdot T(K) \cdot R_S} \quad \left[\frac{V}{\sqrt{Hz}}\right] \quad \text{Thermal noise of } R_S$$

$$(3) \quad e_{R_1 \parallel R_2} = \sqrt{4 \cdot k_B \cdot T(K) \cdot \left[\frac{R_1 \cdot R_2}{R_1 + R_2}\right]} \quad \left[\frac{V}{\sqrt{Hz}}\right] \quad \text{Thermal noise of } R_1 \parallel R_2$$

$$(4) \quad k_B = 1.38065 \cdot 10^{-23} \quad \left[\frac{J}{K}\right] \quad \text{Boltzmann Constant}$$

$$(5) \quad T(K) = 237.15 + T(^{\circ}C) \quad [K] \quad \text{Temperature in kelvins}$$

### (B) Noise in Inverting Gain Configuration



Noise at the output is given as  $E_O$ , where

$$(6) \quad E_O = \left(1 + \frac{R_2}{R_S + R_1}\right) \cdot \sqrt{(e_N)^2 + (e_{R_1 + R_S \parallel R_2})^2 + \left(i_N \cdot \left[\frac{(R_S + R_1) \cdot R_2}{R_S + R_1 + R_2}\right]\right)^2} \quad [V_{RMS}]$$

$$(7) \quad e_{R_1 + R_S \parallel R_2} = \sqrt{4 \cdot k_B \cdot T(K) \cdot \left[\frac{(R_S + R_1) \cdot R_2}{R_S + R_1 + R_2}\right]} \quad \left[\frac{V}{\sqrt{Hz}}\right] \quad \text{Thermal noise of } (R_1 + R_S) \parallel R_2$$

$$(8) \quad k_B = 1.38065 \cdot 10^{-23} \quad \left[\frac{J}{K}\right] \quad \text{Boltzmann Constant}$$

$$(9) \quad T(K) = 237.15 + T(^{\circ}C) \quad [K] \quad \text{Temperature in kelvins}$$

Copyright © 2017, Texas Instruments Incorporated

- (1)  $e_n$  is the voltage noise spectral density of the amplifier. For the TLV2186 series of operational amplifiers,  $e_n = 38 \text{ nV}/\sqrt{\text{Hz}}$  at 1 kHz.
- (2) For additional resources on noise calculations visit [TI Precision Labs](#).

**图 43. Noise Calculation in Gain Configurations**

## 8.2 Typical Applications

### 8.2.1 High-Side Current Sensing

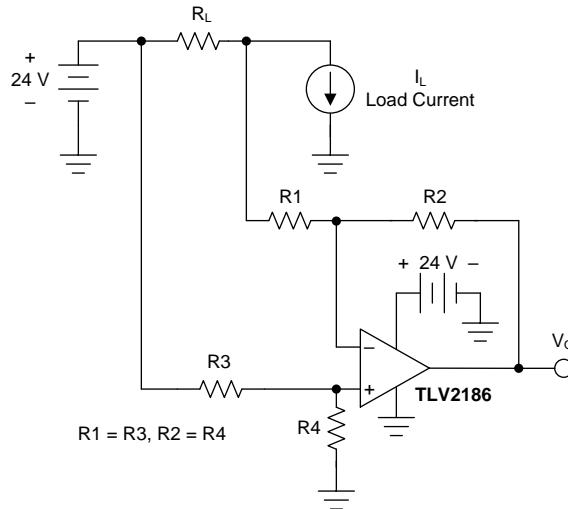


图 44. High-Side Current Monitor

#### 8.2.1.1 Design Requirements

A common systems requirement is to monitor the current being delivered to a load. Monitoring makes sure that normal current levels are being maintained, and also provides an alert if an overcurrent condition occurs.

Fortunately, a relatively simple current monitor solution can be achieved using a precision rail-to-rail input/output op amp such as the TLV2186. This device has an input common-mode voltage ( $V_{CM}$ ) range that extends 200 mV beyond each power supply rail allowing for operation at the supply rail.

The TLV2186 is configured as a difference amplifier with a predetermined gain. The difference amplifier inputs are connected across a sense resistor through which the load current flows. The sense resistor may be connected to the high side or low side of the circuit through which the load current flows. Commonly, high-side current sensing is applied and an applicable TLV2186 configuration is in [图 44](#). Low-side current sensing may be applied as well if the sense resistor can be placed between the load and ground.

Use the following parameters for this design example:

- Single supply: 24 V
- Linear output voltage range: 0.3 V to 3.3 V
- $I_{load}$ : 1 A to 11 A

The design details and equations below can be used to reconfigure this design for different output voltage ranges and current loads.

#### 8.2.1.2 Detailed Design Procedure

Designing a high-side current monitor circuit is straightforward providing the amplifier electrical characteristics are carefully considered so that linear operation is maintained. Other additional considerations, such as the input voltage range of the analog to digital converter (ADC) that follows the current monitor stage, must be kept in mind while configuring the system.

Consider the design of a TLV2186 high-side current monitor with an output voltage range set to be compatible with the input of ADC with an input range of 3.3 V, such as one integrated in a microcontroller. The full-scale input range of such a converter is 0 V to 3.3 V. The TLV2186 can be operated from a single 24-V supply, referenced to ground. Although the TLV2186 is specified as a rail-to-rail input/output (RRIO) amplifier, the linear output operating range (like all amplifiers) does not quite extend all the way to the supply rails. This linear operating range must be taken into consideration.

## Typical Applications (接下页)

The TLV2186 is powered by 24 V; therefore, the device is easily capable of providing the 3.3-V positive level, or even more if the ADC has a wider input range. However, because the TLV2186 output does not swing completely to 0 V, the specified lower swing limit must be observed in the design.

The best measure of an op amp linear output voltage range comes from the open-loop voltage gain ( $A_{OL}$ ) specification listed in the [Electrical Characteristics](#) table. The  $A_{OL}$  test conditions specify a linear swing range 300 mV from each supply rail ( $R_L = 10 \text{ k}\Omega$ ). Therefore, the linear swing limit on the low end ( $V_{oMIN}$ ) is 300 mV, and 3.3 V is the  $V_{oMAX}$  limit, thus yielding an 11:1  $V_{oMAX}$  to  $V_{oMIN}$  ratio. This ratio proves important in determining the difference amplifier operating parameters.

An optimum load current,  $I_{LOAD}$  of 10 A is used as an example. In most applications, however, the ability to monitor current levels well below 10 A is useful. This situation is where the 11:1  $V_{oMAX}$  to  $V_{oMIN}$  ratio is crucial. If 11 A is set as the maximum current, this current must correspond to a 3.3-V output. Using the 11:1 ratio, the minimum current of 1 A corresponds to 300 mV.

Selection of the current sense resistor  $R_S$  comes down to how much voltage drop can be tolerated at maximum current and the permissible power loss, or dissipation. A good compromise for a 10-A sense application is an  $R_S$  of 10 mΩ. That value results in a power dissipation of 1 W, and a 0.1-V drop at 10 amps.

Next, determine the gain of the TLV2186 difference amplifier circuit. The maximum current of 11 A flowing through a 10-mΩ sense resistor results in 110 mV across the resistor. That voltage appears as a differential voltage,  $V_R$ , that is applied across the TLV2186 difference amplifier circuit inputs:

$$V_S = I_L \cdot R_S$$

$$V_S = 11 \text{ A} \cdot 10 \text{ m}\Omega = 110 \text{ mV} \quad (1)$$

The TLV2186 required voltage gain is determined from:

$$G_A = \frac{V_{oMAX}}{V_S}$$

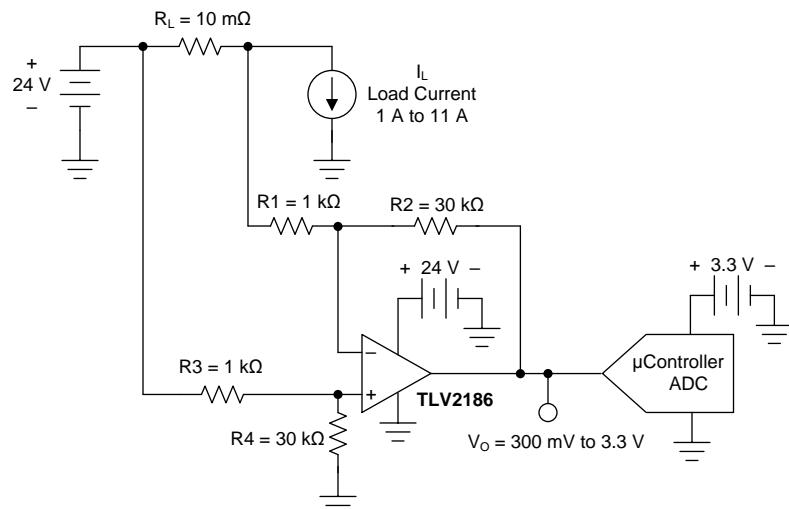
$$G_A = \frac{3.3 \text{ V}}{0.11 \text{ V}} = 30 \frac{\text{V}}{\text{V}} \quad (2)$$

Now, checking the  $V_{oMIN}$  using  $I_L = 1 \text{ A}$ :

$$V_{oMIN} = G_A \cdot I_{SMIN} \cdot R_S$$

$$V_{oMIN} = 30 \frac{\text{V}}{\text{V}} \cdot 1 \text{ A} \cdot 10 \text{ m}\Omega = 300 \text{ mV} \quad (3)$$

The complete TLV2186 high-side current monitor is shown in [图 45](#). The circuit is capable of monitoring a current range of < 1 A to 11 A, with a  $V_{CM}$  very close to the 24-V supply voltage.



**图 45. TLV2186 Configured as a High-Side Current Monitor**

## Typical Applications (接下页)

In this example, the TLV2186 output voltage is intentionally limited to 3.3 V. However, because of the 24-V supply, the output voltage could be much higher to allow for a higher-voltage data converter with a higher dynamic range.

The circuit in [图 45](#) was checked using the TINA Spice circuit simulation tool to verify the correct operation of the TLV2186 high-side current monitor. The simulation results are seen in [图 46](#). The performance is exactly as expected. Upon careful inspection of the plots, one possible surprise is that  $V_O$  continues towards zero as the sense current drops below 1 A, where  $V_O$  is 300 mV and less.

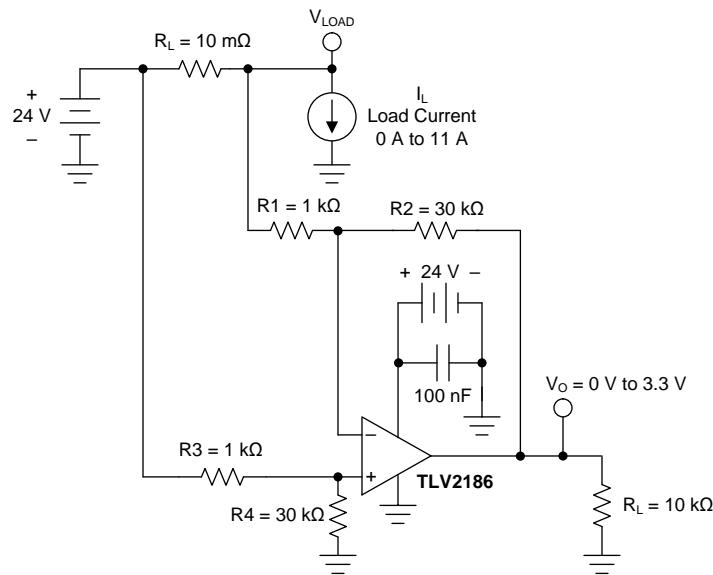


图 46. TLV2186 High-Side Current-Monitor Simulation Schematic

The TLV2186 output, as well as other CMOS output amplifiers, often swing closer to 0 V than the linear output parameters suggest. The [Electrical Characteristics](#) table lists under the OUTPUT subsection  $V_O$ , which is an *output slam* to the rail measure. It is not an indication of the linear output range, but instead how close the output can move towards the supply rail. In that region, the amplifier output approaches saturation, and the amplifier ceases to operate linearly. Thus, in the current-monitor application, the current-measurement capability may continue well below the 300 mV output level. However, keep in mind that the linearity errors are becoming large.

Lastly, some notes about maximizing the high-side current monitor performance:

- All resistor values are critical for accurate gain results. The resistor pairs of [R1 and R3] and [R2 and R4] must be matched as closely as possible to minimize common-mode mismatch error. Use a 0.1% tolerance, or better. Often, selecting two adjacent resistors on a reel provides close matching compared to random selection.
- Keep the closed-loop gain,  $G_A$ , to which the TLV2186 difference amplifier is set, to a reasonable value. Doing so reduces gain error and can be used to maximize bandwidth. A  $G_A$  of 30 V/V is used in the example.
- Although current monitoring is often used for monitoring dc supply currents, ac current can also be monitored. The –3-dB bandwidth, or upper cutoff frequency, of the circuit of is:

$$f_H = \frac{GBW}{\text{Noise Gain}}$$

where

- GBW is the amplifier unity gain bandwidth; 750 kHz for the TLV2186.
- Noise gain is equal to the gain as seen looking into the op amp noninverting input, as shown in [公式 5](#). (4)

$$G_{NG} = 1 + \frac{R2}{R1} \quad (5)$$

## Typical Applications (接下页)

For the TLV2186 circuit in [图 45](#):

$$G_{NG} = 1 + \frac{30 \text{ k}\Omega}{1 \text{ k}\Omega} = 31 \frac{\text{V}}{\text{V}}$$

$$f_H = \frac{750 \text{ kHz}}{31} = 24.2 \text{ kHz}$$

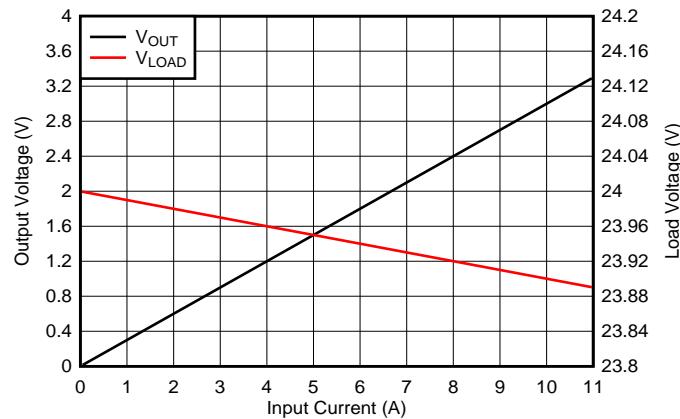
Make sure that the amplifier slew rate is sufficient to support the expected output voltage swing range and waveform. Also, if a single power supply such as 24 V is used, the ac power source applied to the sense input must have a positive dc component to keep the  $V_{CM}$  above 0 V. The input voltage cannot drop below 0 V if normal operation is to be maintained.

The TLV2186 output can attain a 0 V output level if a small negative voltage is used to power the  $V_-$  pin instead of ground. The LM7705 is a switched capacitor voltage inverter with a regulated, low-noise,  $-0.23\text{-V}$  fixed voltage output. Powering the TLV2186  $V_-$  pin at this level approximately matches the 300-mV linear output voltage swing lower limit, thus extending the output swing to 0 V, or very near 0 V. Doing so greatly improves the resolution at low sense current levels.

The LM7705 requires only about 78  $\mu\text{A}$  of quiescent current, but be aware that the specified supply range is 3 V to 5.25 V. The 3.3-V or 5-V supply used by the ADC could be tapped as a power source.

For more information about amplifier-based, high-side current monitors, see the [TI Analog Engineer's Circuit Cookbook: Amplifiers](#).

### 8.2.1.3 Application Curve

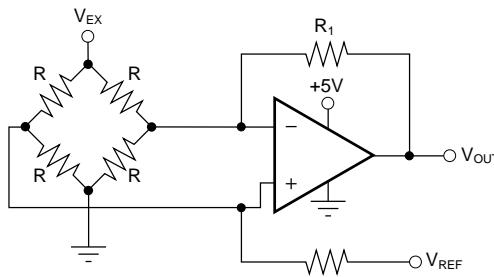


**图 47. High-Side Results**

## Typical Applications (接下页)

### 8.2.2 Bridge Amplifier

图 48 shows the basic configuration for a bridge amplifier. Click the following link to download the TINA-TI file: [Bridge Amplifier Circuit](#).



Copyright © 2017, Texas Instruments Incorporated

图 48. Bridge Amplifier

### 8.2.3 Low-Side Current Monitor

图 49 shows the TLV2186 configured in a low-side current-sensing application. The load current ( $I_{LOAD}$ ) creates a voltage drop across the shunt resistor ( $R_{SHUNT}$ ). This voltage is amplified by the TLV2186, with a gain of 201. In this example, the load current is set from 0 A to 500 mA, and corresponds to an output voltage range from 0 V to 10 V. The output range can be adjusted by changing the shunt resistor or gain of the configuration. Click the following link to download the TINA-TI file: [Current-Sensing Circuit](#).

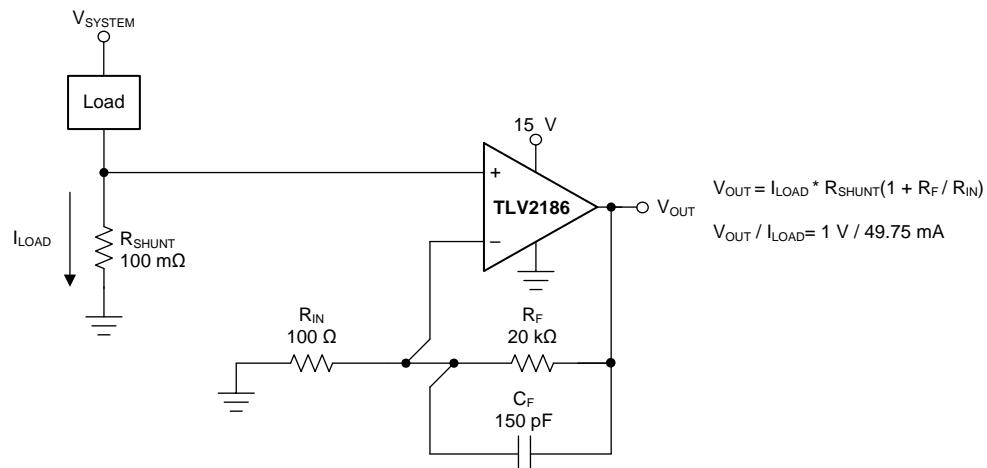
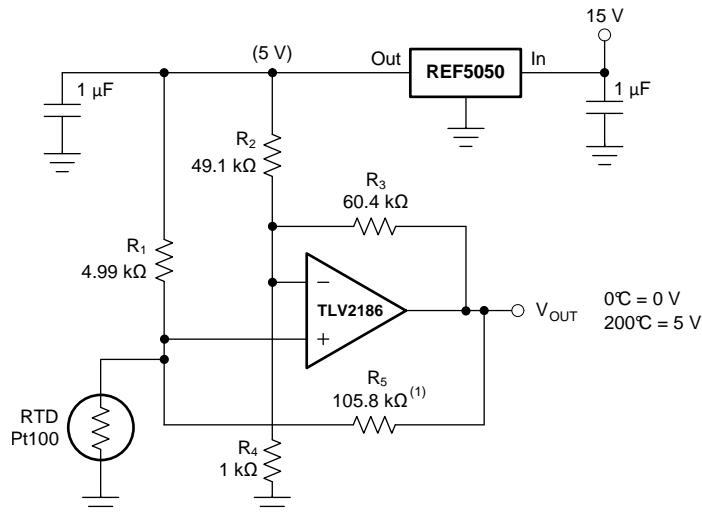


图 49. Low-Side Current Monitor

## Typical Applications (接下页)

#### 8.2.4 RTD Amplifier With Linearization

See the *Analog Linearization of Resistance Temperature Detectors* technical brief for an in-depth analysis of Figure 50. Click the following link to download the TINA-TI file: [RTD Amplifier with Linearization](#).



(1)  $R_5$  provides positive-varying excitation to linearize output.

图 50. RTD Amplifier With Linearization

## 9 Power Supply Recommendations

The TLV2186 is specified for operation from 4.5 V to 24 V ( $\pm 2.25$  V to  $\pm 12$  V); many specifications apply from  $-40^\circ\text{C}$  to  $+125^\circ\text{C}$ . The *Typical Characteristics* presents parameters that can exhibit significant variance with regard to operating voltage or temperature.

## CAUTION

Supply voltages larger than 40 V can permanently damage the device (see the [Absolute Maximum Ratings](#)).

Place  $0.1\text{-}\mu\text{F}$  bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see the [Layout](#) section.

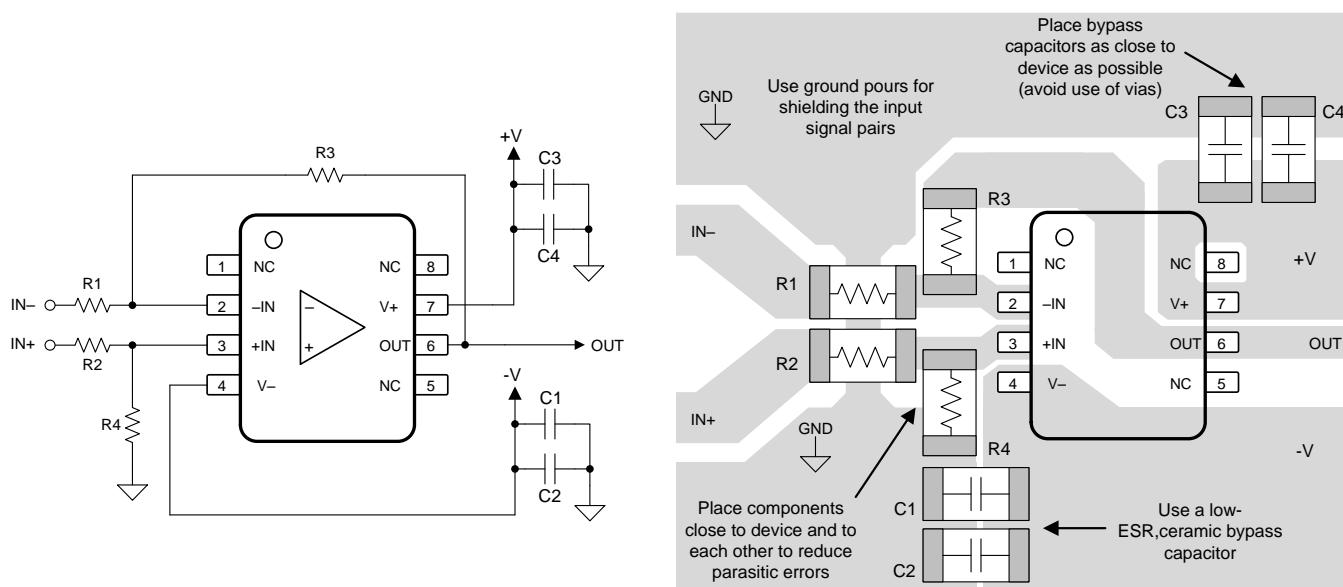
## 10 Layout

### 10.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including:

- For the lowest offset voltage, avoid temperature gradients that create thermoelectric (Seebeck) effects in the thermocouple junctions formed from connecting dissimilar conductors. Also:
  - Use low thermoelectric-coefficient conditions (avoid dissimilar metals).
  - Thermally isolate components from power supplies or other heat sources.
  - Shield operational amplifier and input circuitry from air currents, such as cooling fans.
- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and the op amp itself. Bypass capacitors reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
  - Connect low-ESR, 0.1- $\mu$ F ceramic bypass capacitors between each supply pin and ground, placed as close as possible to the device. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital and analog grounds paying attention to the flow of the ground current. For more detailed information, see [The PCB is a component of op amp design](#).
- To reduce parasitic coupling, run the input traces as far away as possible from the supply or output traces. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better as opposed to in parallel with the noisy trace.
- Place the external components as close as possible to the device. As illustrated in [图 51](#), keep the feedback resistor (R3) and gain resistor (R4) close to the inverting input to minimize parasitic capacitance.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.
- For best performance, clean the PCB following board assembly.
- Any precision integrated circuit may experience performance shifts due to moisture ingress into the plastic package. Following any aqueous PCB cleaning process, bake the PCB assembly to remove moisture introduced into the device packaging during the cleaning process. A low-temperature, post-cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

## 10.2 Layout Example



Copyright © 2017, Texas Instruments Incorporated

图 51. Operational Amplifier Board Layout for Difference Amplifier Configuration

## 11 器件和文档支持

### 11.1 器件支持

#### 11.1.1 开发支持

##### 11.1.1.1 TINA-TI™ (免费软件下载)

TINA-TI™ 是一款基于 SPICE 引擎的电路仿真程序，简单易用并且功能强大。TINA-TI™ 是 TINA™ 软件的一款免费全功能版本，除了一系列无源和有源模型外，此版本软件还预先载入了一个宏模型库。TINA-TI™ 提供所有传统的 SPICE 直流、瞬态和频域分析，以及其他设计功能。

TINA-TI™ 提供全面的后处理能力，便于用户以多种方式获得结果，用户可从 Analog eLab Design Center (模拟电子实验室设计中心) [免费下载](#)。虚拟仪器提供选择输入波形和探测电路节点、电压以及波形的功能，从而构建一个动态的快速入门工具。

注

这些文件需要安装 TINA 软件 (由 DesignSoft™ 提供) 或者 TINA-TI™ 软件。请下载 [TINA-TI™ 文件夹](#) 中的免费 TINA-TI™ 软件。

##### 11.1.1.2 TI 高精度设计

欲获取 TI 高精度设计，请访问 <http://www.ti.com.cn/ww/analog/precision-designs/>。TI 高精度设计是由 TI 公司高精度模拟应用专家创建的模拟解决方案，提供了许多实用电路的工作原理、组件选择、仿真、完整印刷电路板 (PCB) 电路原理图和布局布线、物料清单以及性能测量结果。

### 11.2 文档支持

#### 11.2.1 相关文档

请参阅如下相关文档：

- 德州仪器 (TI)，[《零漂移放大器：特性和优势》](#)
- 德州仪器 (TI)，[《运算放大器设计组件 PCB》](#)
- 德州仪器 (TI)，[《适合所有人的运算放大器》](#)
- 德州仪器 (TI)，[《运算放大器增益稳定性，第 3 部分：交流增益误差分析》](#)
- 德州仪器 (TI)，[《运算放大器增益稳定性，第 2 部分：直流增益误差分析》](#)
- 德州仪器 (TI)，[《在全差分有源滤波器中使用无限增益、MFB 滤波器拓扑》](#)
- 德州仪器 (TI)，[《运算放大器性能分析》](#)
- 德州仪器 (TI)，[《运算放大器的单电源运行》](#)
- 德州仪器 (TI)，[《放大器调优》](#)
- 德州仪器 (TI)，[《无铅组件涂层的储存寿命评估》](#)
- 德州仪器 (TI)，[《反馈曲线图定义运算放大器交流性能》](#)
- 德州仪器 (TI)，[《运算放大器的 EMI 抑制比》](#)
- 德州仪器 (TI)，[《电阻式温度检测器的模拟线性化》](#)
- 德州仪器 (TI)，[《TI 精密设计 TIPD102 高侧电压-电流 \(V-I\) 转换器》](#)

### 11.3 接收文档更新通知

要接收文档更新通知，请导航至 [TI.com.cn](http://TI.com.cn) 上的器件产品文件夹。单击右上角的通知我进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

### 11.4 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

[TI E2E™ Online Community](#) [TI's Engineer-to-Engineer \(E2E\) Community](#). Created to foster collaboration

## 社区资源 (接下页)

among engineers. At [e2e.ti.com](http://e2e.ti.com), you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

## 11.5 商标

TINA-TI, E2E are trademarks of Texas Instruments.

Bluetooth is a registered trademark of Bluetooth SIG, Inc.

TINA, DesignSoft are trademarks of DesignSoft, Inc.

All other trademarks are the property of their respective owners.

## 11.6 静电放电警告

 ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

 ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

## 11.7 Glossary

[SLYZ022 — TI Glossary](#).

This glossary lists and explains terms, acronyms, and definitions.

## 12 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

**PACKAGING INFORMATION**

| Orderable Device | Status<br>(1) | Package Type | Package Drawing | Pins | Package Qty | Eco Plan<br>(2) | Lead finish/<br>Ball material<br>(6) | MSL Peak Temp<br>(3) | Op Temp (°C) | Device Marking<br>(4/5) | Samples   |
|------------------|---------------|--------------|-----------------|------|-------------|-----------------|--------------------------------------|----------------------|--------------|-------------------------|---|
| TLV2186IDR       | ACTIVE        | SOIC         | D               | 8    | 2500        | RoHS & Green    | NIPDAU                               | Level-2-260C-1 YEAR  | -40 to 125   | T2186                   | <span style="background-color: red; color: white; padding: 2px;">Samples</span> |
| TLV2186IDSGR     | ACTIVE        | WSON         | DSG             | 8    | 3000        | RoHS & Green    | NIPDAU                               | Level-1-260C-UNLIM   | -40 to 125   | PVDY                    | <span style="background-color: red; color: white; padding: 2px;">Samples</span> |
| TLV2186IDSGT     | ACTIVE        | WSON         | DSG             | 8    | 250         | RoHS & Green    | NIPDAU                               | Level-1-260C-UNLIM   | -40 to 125   | PVDY                    | <span style="background-color: red; color: white; padding: 2px;">Samples</span> |

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

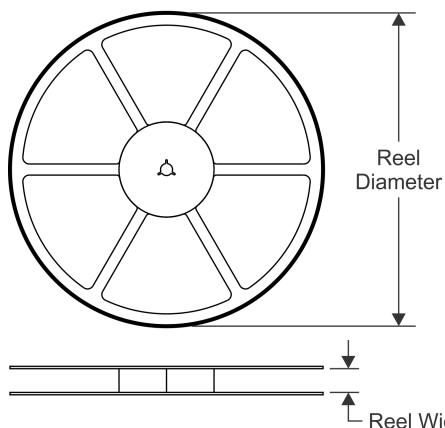
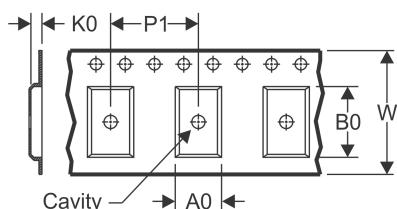
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

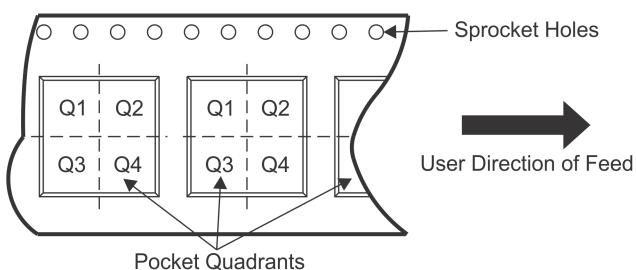
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

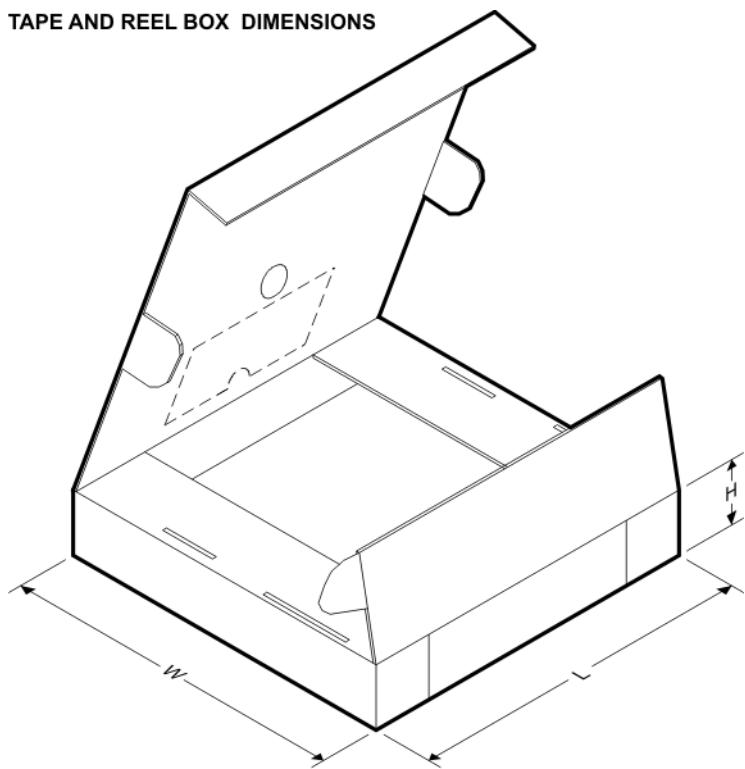
**TAPE AND REEL INFORMATION**
**REEL DIMENSIONS**

**TAPE DIMENSIONS**


|    |   |
|----|---|
| A0 | Dimension designed to accommodate the component width     |
| B0 | Dimension designed to accommodate the component length    |
| K0 | Dimension designed to accommodate the component thickness |
| W  | Overall width of the carrier tape                         |
| P1 | Pitch between successive cavity centers                   |

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

| Device       | Package Type | Package Drawing | Pins | SPQ  | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|--------------|--------------|-----------------|------|------|--------------------|--------------------|---------|---------|---------|---------|--------|---------------|
| TLV2186IDR   | SOIC         | D               | 8    | 2500 | 330.0              | 12.4               | 6.4     | 5.2     | 2.1     | 8.0     | 12.0   | Q1            |
| TLV2186IDSGR | WSON         | DSG             | 8    | 3000 | 180.0              | 8.4                | 2.3     | 2.3     | 1.15    | 4.0     | 8.0    | Q2            |
| TLV2186IDSGT | WSON         | DSG             | 8    | 250  | 180.0              | 8.4                | 2.3     | 2.3     | 1.15    | 4.0     | 8.0    | Q2            |

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

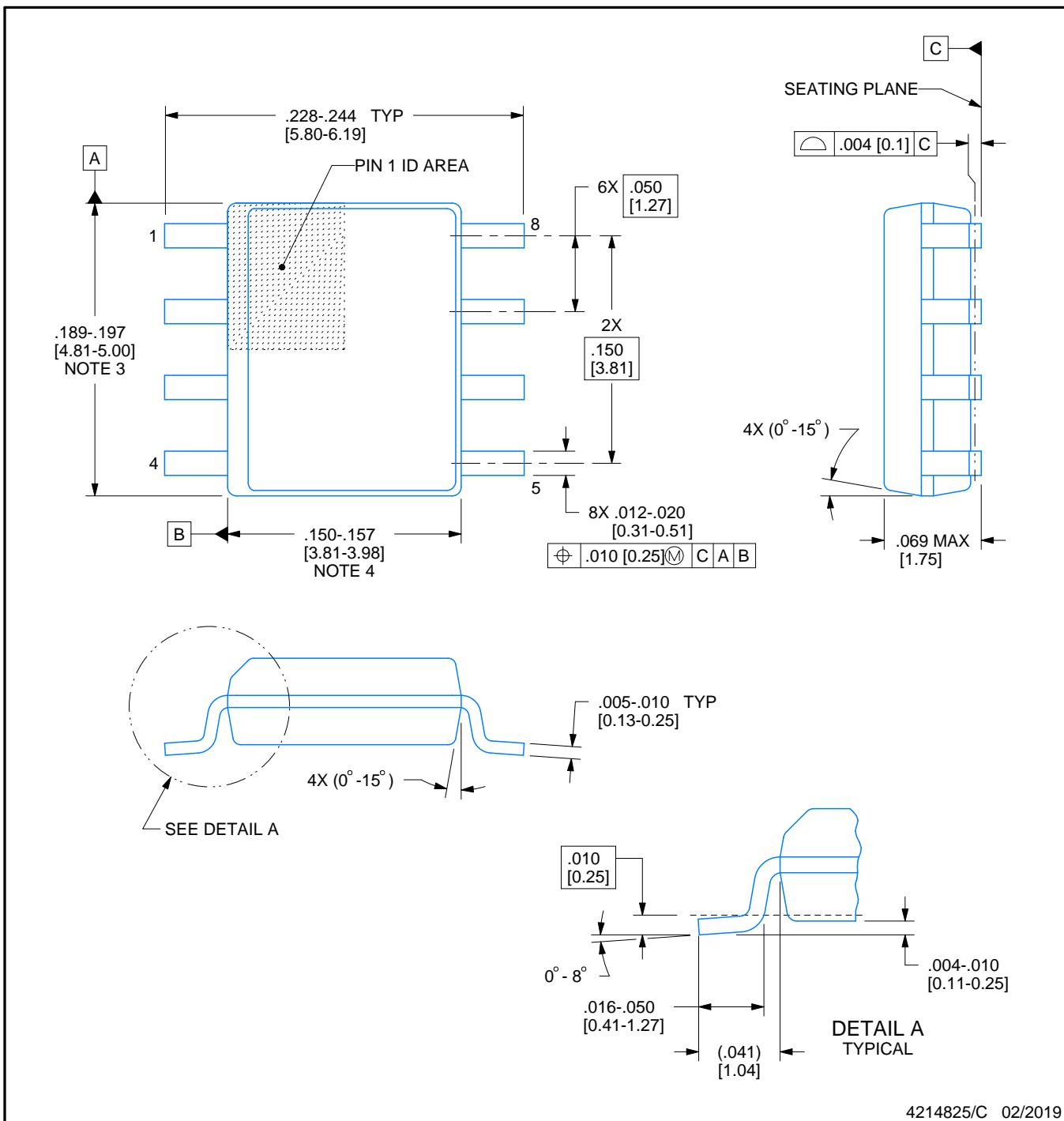
| Device       | Package Type | Package Drawing | Pins | SPQ  | Length (mm) | Width (mm) | Height (mm) |
|--------------|--------------|-----------------|------|------|-------------|------------|-------------|
| TLV2186IDR   | SOIC         | D               | 8    | 2500 | 853.0       | 449.0      | 35.0        |
| TLV2186IDSGR | WSON         | DSG             | 8    | 3000 | 210.0       | 185.0      | 35.0        |
| TLV2186IDSGT | WSON         | DSG             | 8    | 250  | 210.0       | 185.0      | 35.0        |



# PACKAGE OUTLINE

## SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



### NOTES:

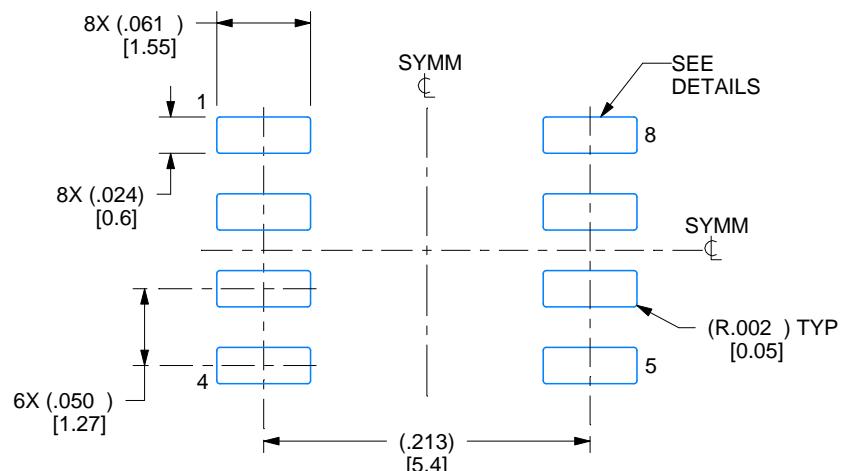
1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

# EXAMPLE BOARD LAYOUT

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE  
BASED ON .005 INCH [0.125 MM] THICK STENCIL  
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

# GENERIC PACKAGE VIEW

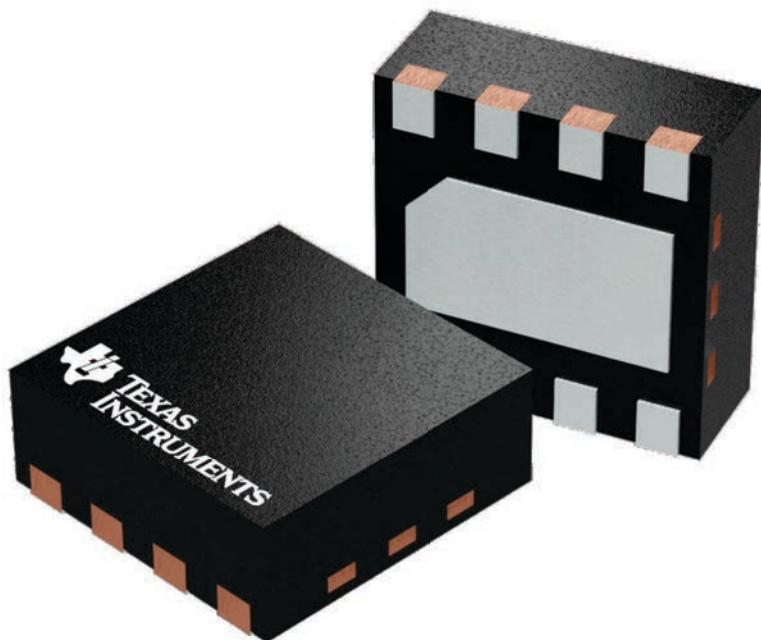
## DSG 8

## WSON - 0.8 mm max height

2 x 2, 0.5 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

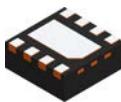
This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.



4224783/A

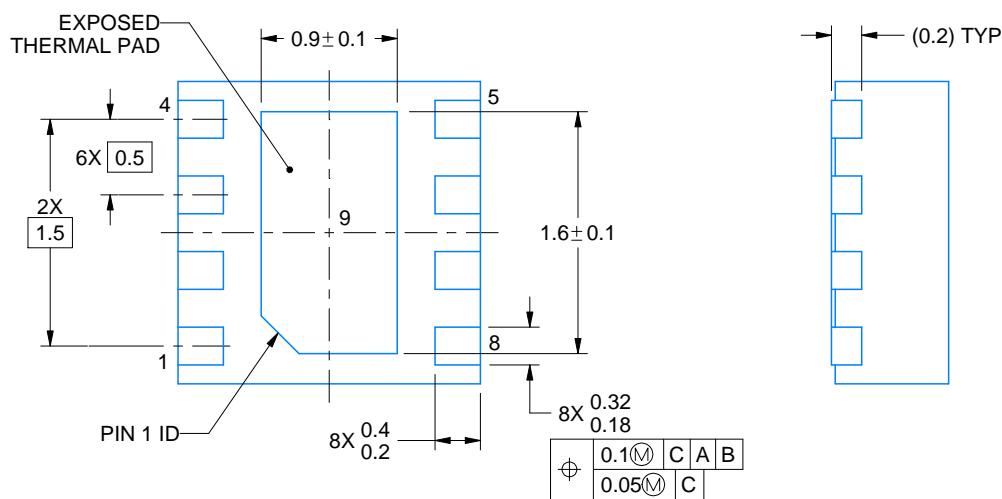
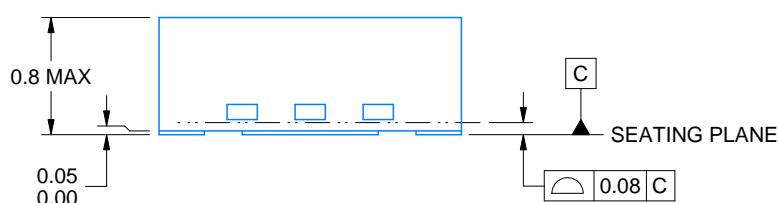
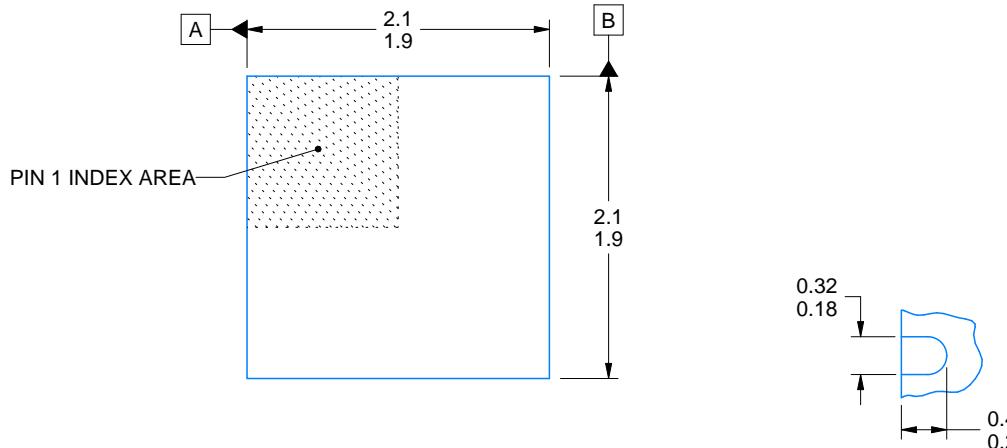
# PACKAGE OUTLINE

DSG0008A



WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



4218900/D 04/2020

## NOTES:

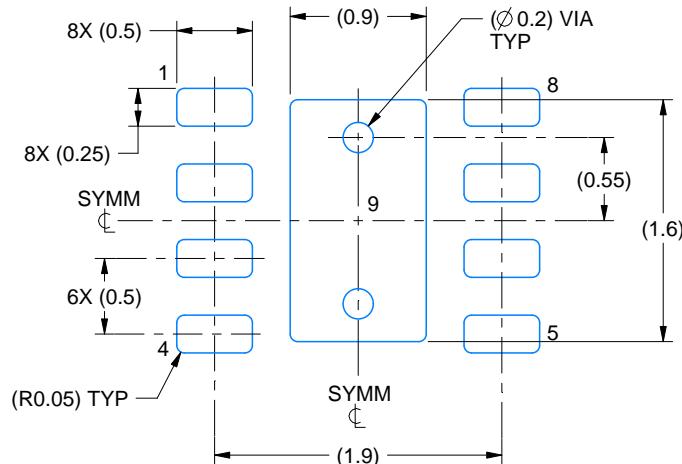
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

# EXAMPLE BOARD LAYOUT

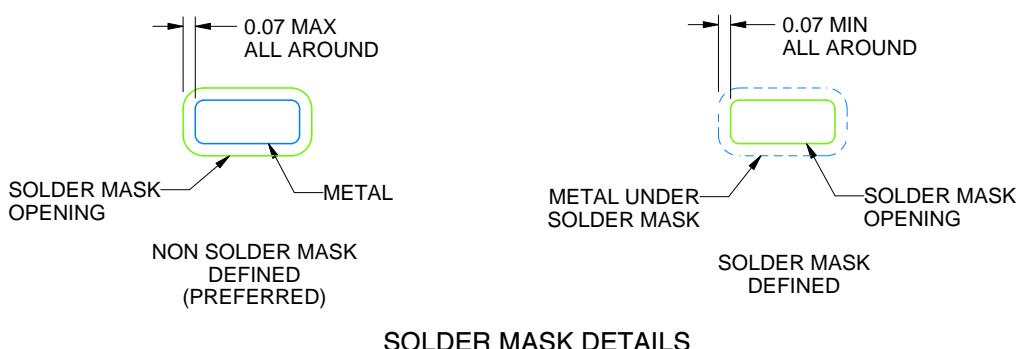
DSG0008A

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE  
SCALE:20X



SOLDER MASK DETAILS

4218900/D 04/2020

NOTES: (continued)

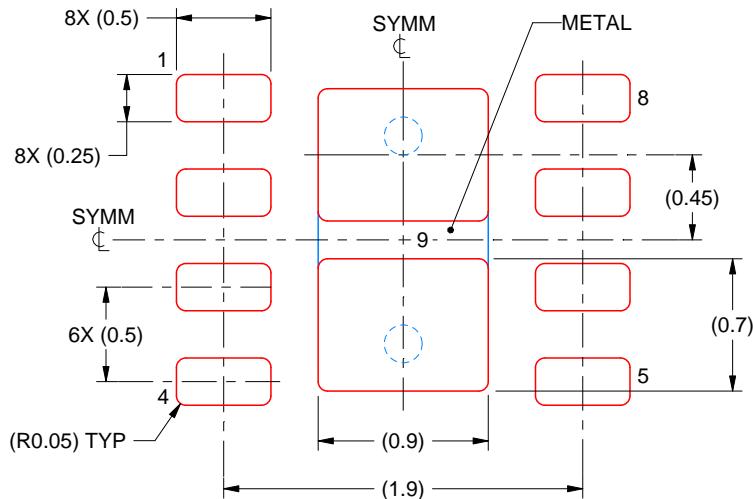
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/slua271](http://www.ti.com/lit/slua271)).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

# EXAMPLE STENCIL DESIGN

DSG0008A

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 9:  
87% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE  
SCALE:25X

4218900/D 04/2020

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

## 重要声明和免责声明

TI 提供技术和可靠性数据（包括数据表）、设计资源（包括参考设计）、应用或其他设计建议、网络工具、安全信息和其他资源，不保证没有瑕疵且不做出任何明示或暗示的担保，包括但不限于对适销性、某特定用途方面的适用性或不侵犯任何第三方知识产权的暗示担保。

这些资源可供使用 TI 产品进行设计的熟练开发人员使用。您将自行承担以下全部责任：(1) 针对您的应用选择合适的 TI 产品，(2) 设计、验证并测试您的应用，(3) 确保您的应用满足相应标准以及任何其他安全、安保或其他要求。这些资源如有变更，恕不另行通知。TI 授权您仅可将这些资源用于研发本资源所述的 TI 产品的应用。严禁对这些资源进行其他复制或展示。您无权使用任何其他 TI 知识产权或任何第三方知识产权。您应全额赔偿因在这些资源的使用中对 TI 及其代表造成任何索赔、损害、成本、损失和债务，TI 对此概不负责。

TI 提供的产品受 TI 的销售条款 (<https://www.ti.com/cn/zh-cn/legal/termsofsale.html>) 或 [ti.com.cn](https://ti.com/cn) 上其他适用条款/TI 产品随附的其他适用条款的约束。TI 提供这些资源并不会扩展或以其他方式更改 TI 针对 TI 产品发布的适用的担保或担保免责声明。

邮寄地址：上海市浦东新区世纪大道 1568 号中建大厦 32 楼，邮政编码：200122  
Copyright © 2021 德州仪器半导体技术（上海）有限公司